

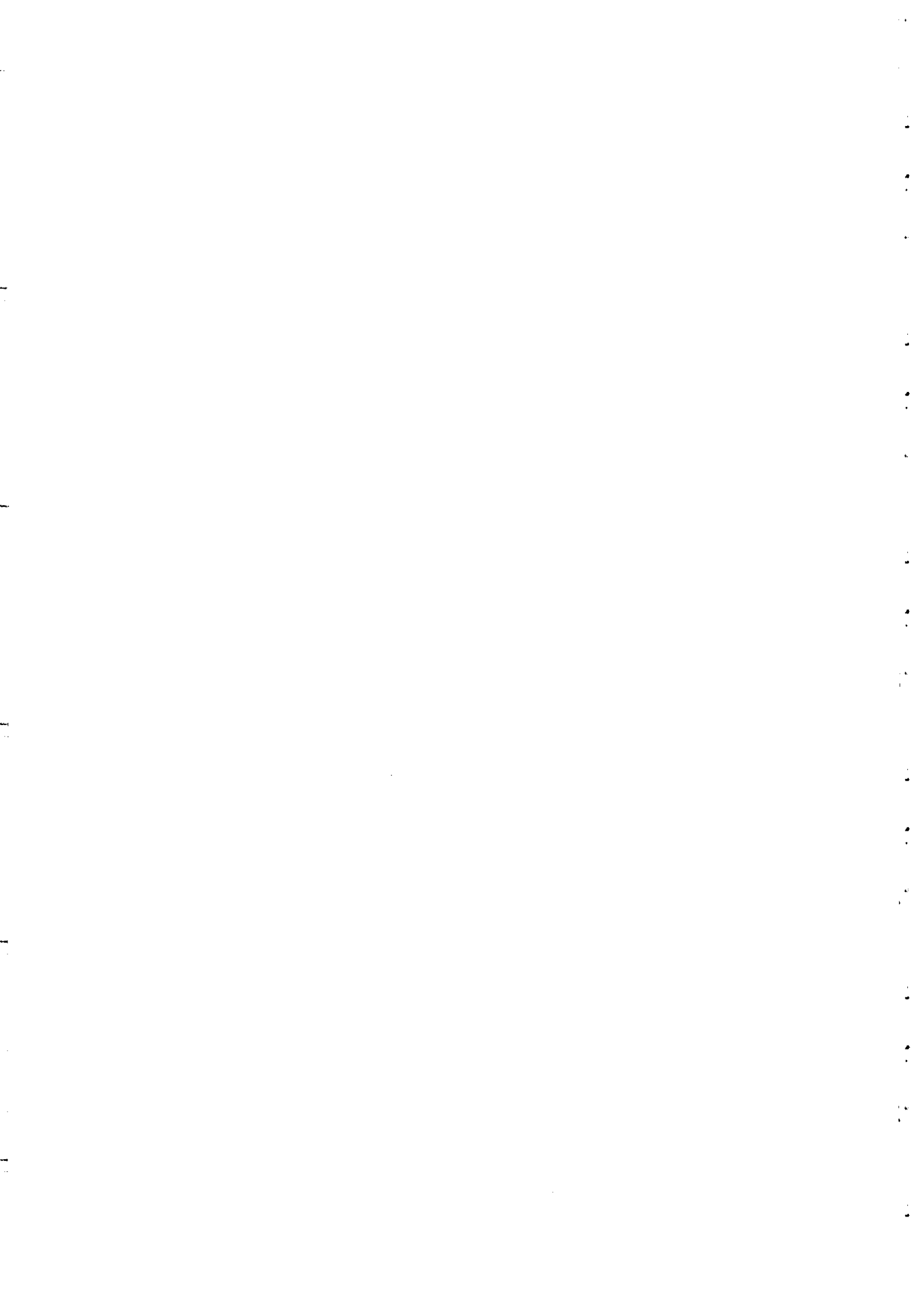
Winter College on Optics and Photonics
7 - 25 February 2000

1218-14

"Micro-Optics & Optical Nanostructures"

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Institut de Microchnique
Univ. Neuchâtel
Switzerland

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Micro-Optics & Optical Nanostructures

H. P. Herzig

Institut de Microchnique, Université de Neuchâtel

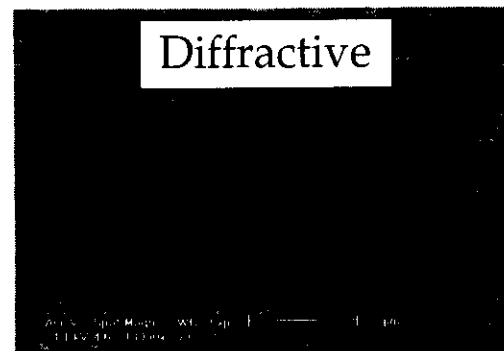
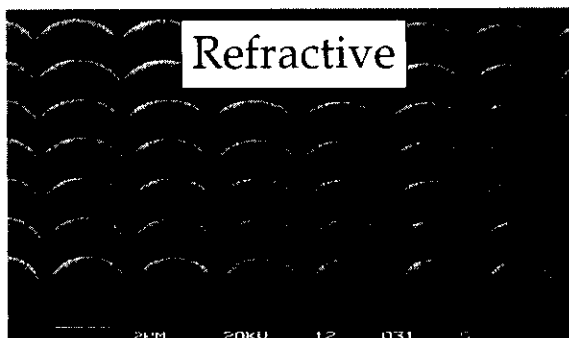
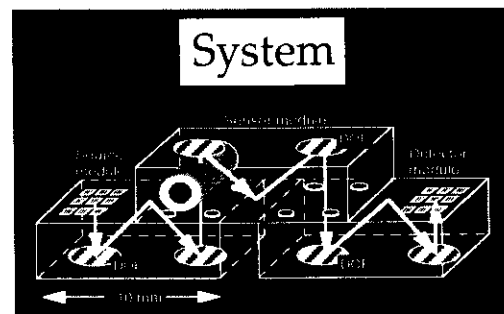
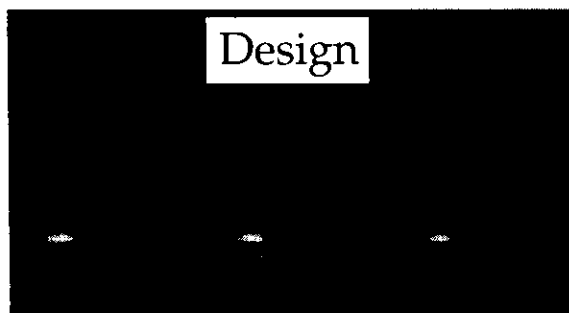
<http://www-imt.unine.ch/>

hanspeter.herzig@imt.unine.ch



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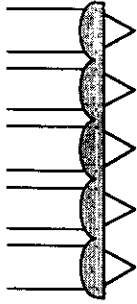


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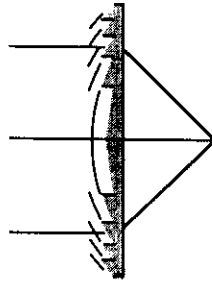
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Micro-optical elements

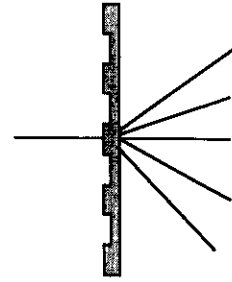
Free-space



microlens array



diffractive optical element



optimized grating

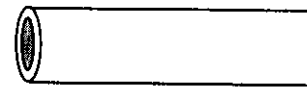
Integrated



grating coupler



integrated optics



fiber optics

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Definition of micro-optics

- Optical elements with structures in the sub-mm and sub- μ range, which are fabricated mainly by lithographic methods
- Systems based on these elements

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Realization of micro-optical elements

- Computer generated data
- Conversion of data into an optical element by lithographic methods
- Transfer of the structure in a rigid or transparent material (etching)
- Replication

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Micro-Optics: contents

- Diffraction - refraction
- Design fundamentals of micro-optical elements
- Fabrication techniques
- Aperture modulated diffusers (AMDs)
- Color fan-out elements
- Grating spectrometer
- Fourier spectrometer
- Lab on chip

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Refractive and diffractive micro-optics: theory

- Fundamentals of refraction and diffraction
- Complex amplitude transmittance
 $t(x,y) = \exp[\Phi(x,y)]$
- Implementation of phase function $\Phi(x,y)$
- Optimum design
- Diffraction elements - refractive elements

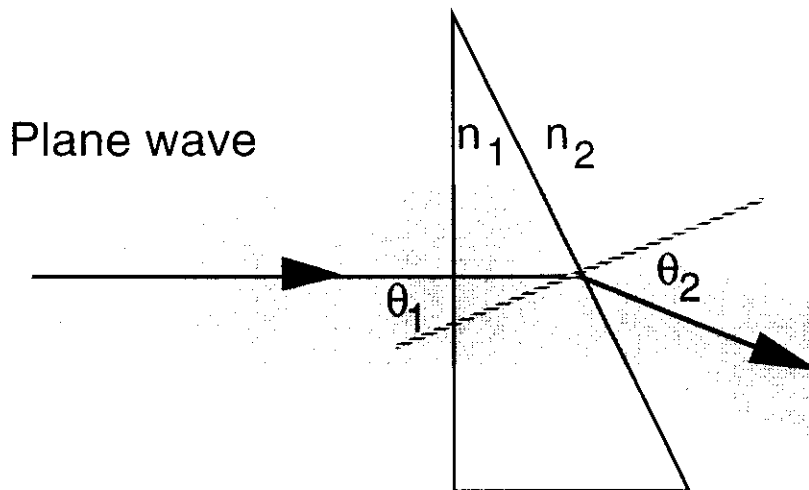
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Refraction

$$n_1(\lambda) \sin \theta_1 = n_2(\lambda) \sin \theta_2$$



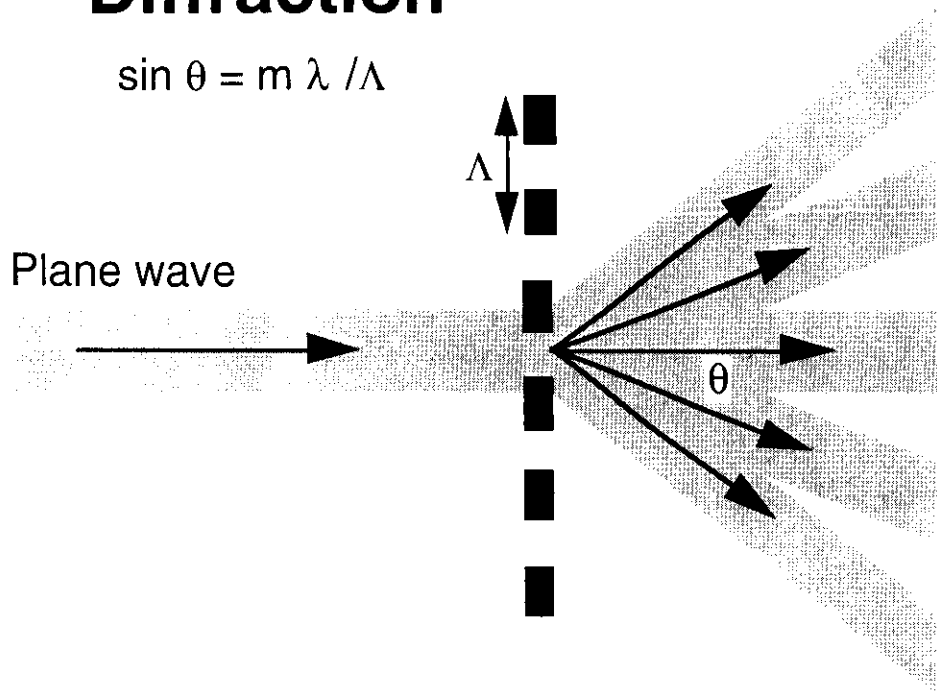
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Diffraction

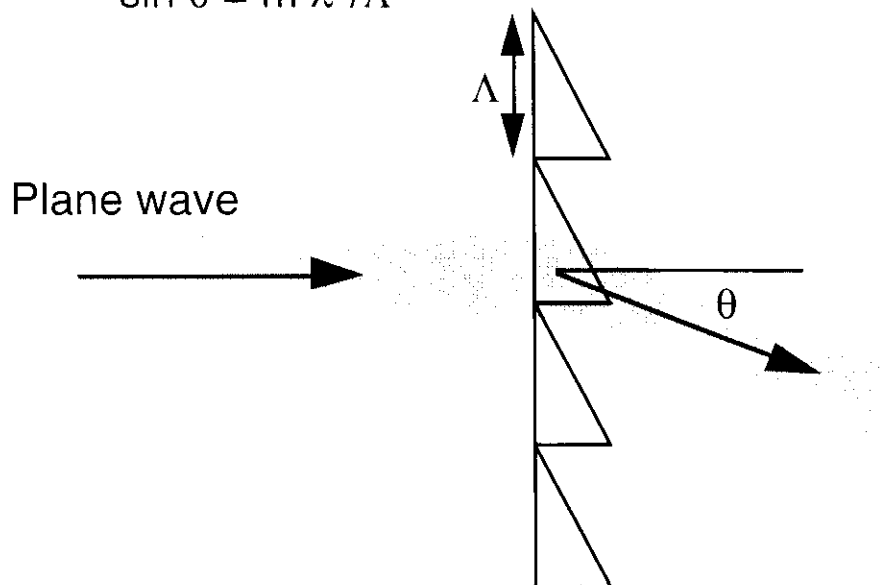
$$\sin \theta = m \lambda / \Lambda$$



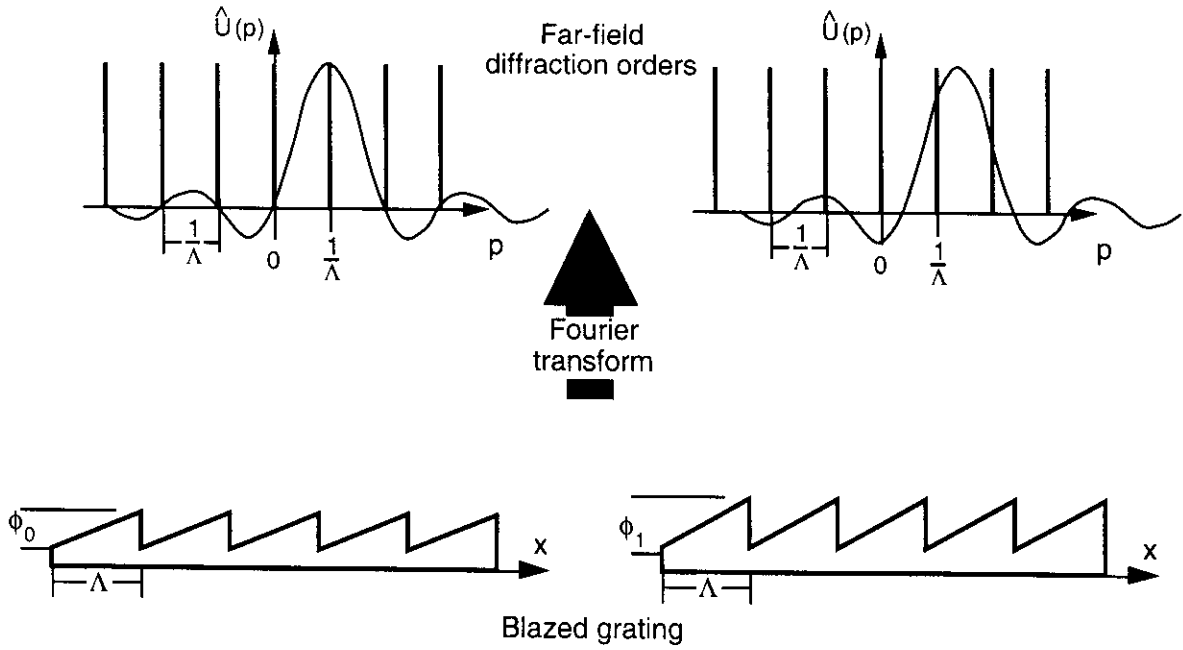
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Diffraction

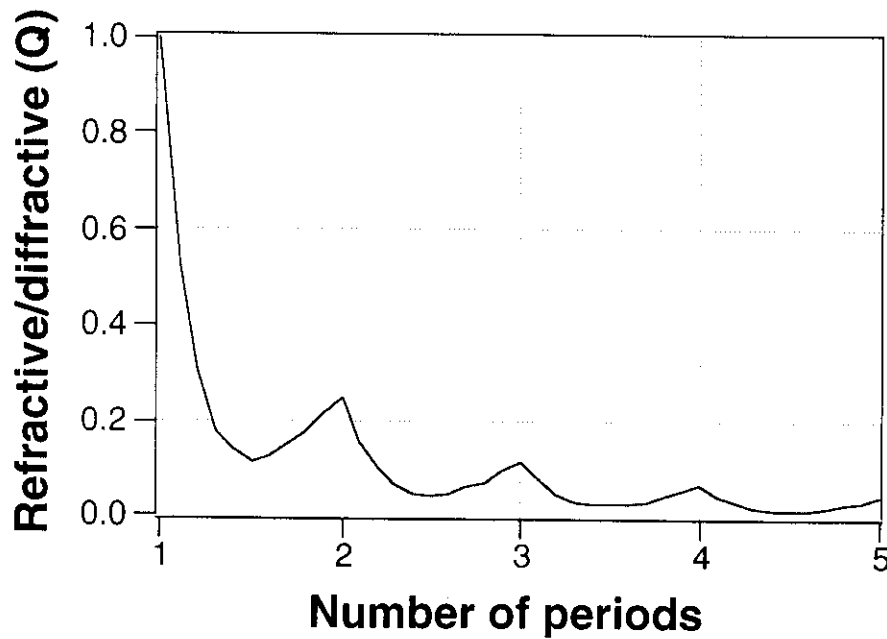
$$\sin \theta = m \lambda / \Lambda$$



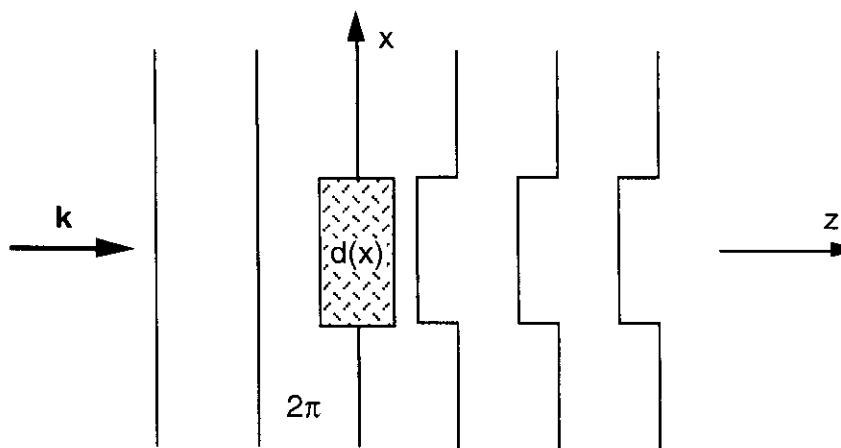
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Refractive-diffractive properties of blazed grating (shrinkage error 10 %)



Complex amplitude transmittance



$$U_2 = U_1 \exp[i\Phi(x)] \quad \text{with} \quad \Phi(x) = d(x) (n - 1) (2\pi/\lambda)$$

$$U_2 = t(x) U_1 \quad \text{transmittance: } t(x) = \exp[i\Phi(x)]$$

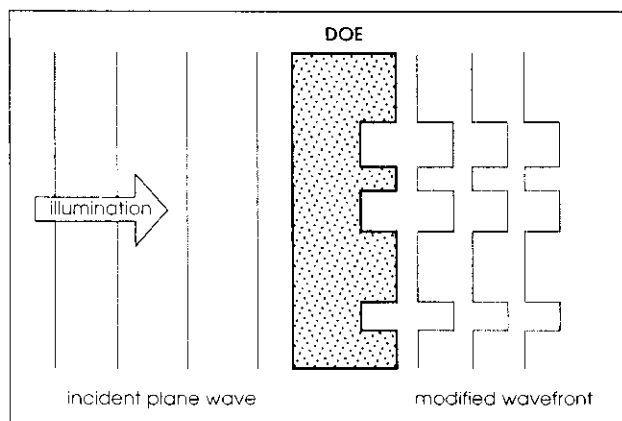


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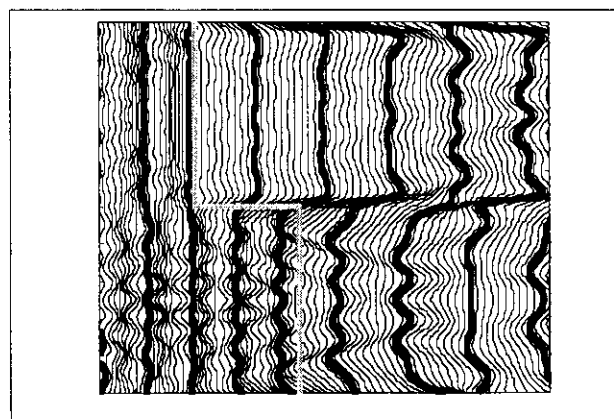
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Why rigorous diffraction theory?

The interaction of light with structures having geometrical features in the order of the wavelength can not be described with classical scalar (thin-) diffraction models, but ask for



thin diffraction theory



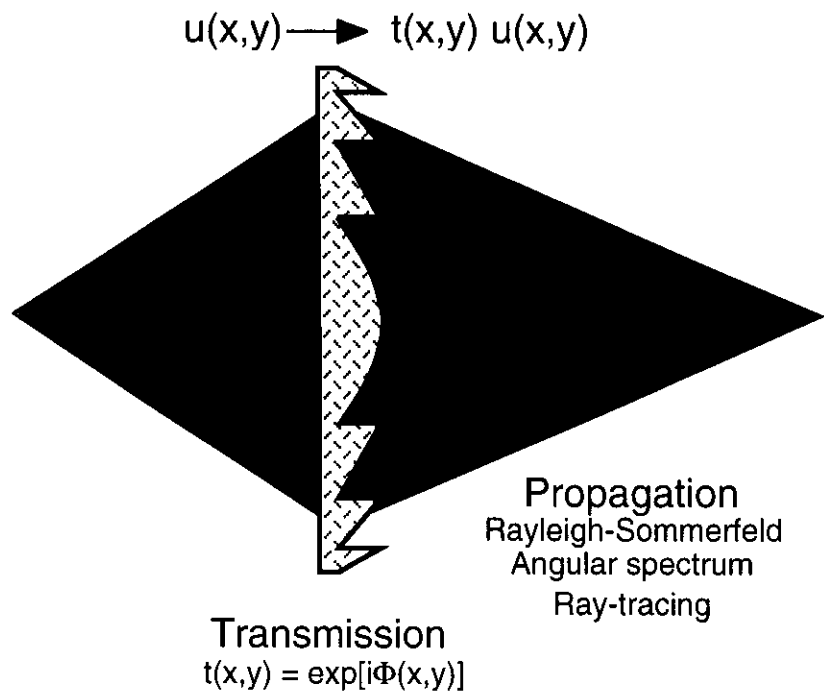
rigorous diffraction theory



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Transmission and propagation



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Calculation of the phase function

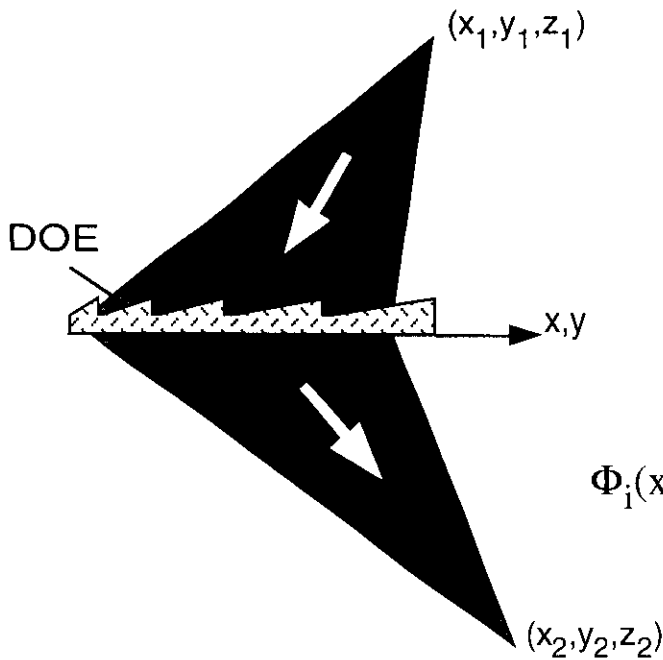
A thin phase element that is illuminated by an incident wave $\Phi_{in}(x,y)$ generates an output wave $\Phi_{out}(x,y)$. The wavefront conversion is described by

$$\Phi_{out}(x,y) = \Phi_{in}(x,y) + \Phi(x,y)$$

$$\Phi(x,y) = \Phi_{out}(x,y) - \Phi_{in}(x,y)$$

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Diffractive lens which connects an object point (x_1, y_1, z_1) with an image point (x_2, y_2, z_2) .

$$\Phi_i(x, y) = \frac{2\pi}{\lambda_0} \sqrt{(x - x_i)^2 + (y - y_i)^2 + (z_i)^2}$$

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In general, the optical task is more complex, e.g., if an extended object has to be imaged. In that case, the DOE phase function $\Phi(x, y)$ is typically described by a polynomial:

$$\Phi(x, y) = \frac{2\pi}{\lambda} \sum_{m, n} a_{mn} x^m y^n$$

The DOE is then optimized by optimizing the polynomial coefficients $a_{m n}$.

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Implementation of the phase function as DOE

In order to realize a diffractive element, the phase function Φ is wrapped to an interval between 0 and an integer multiple of 2π .

Phase profile: $\Psi(x,y) = [\Phi(x,y) + \varphi_0] \bmod 2\pi$

Relief profile: $h(x,y) = [\Psi(x,y)/2\pi][\lambda_0 / (n(\lambda_0) - 1)]$

φ_0 constant phase offset.

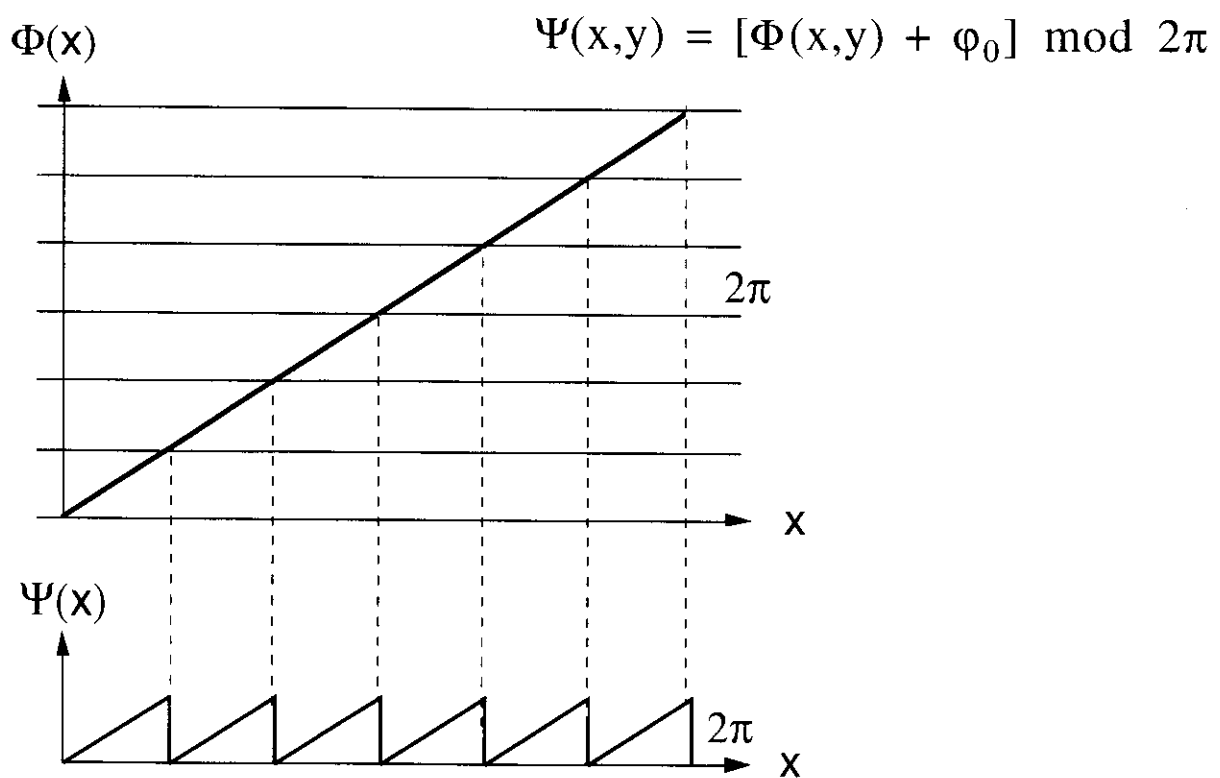
n refractive index of the grating material

λ_0 design wavelength.



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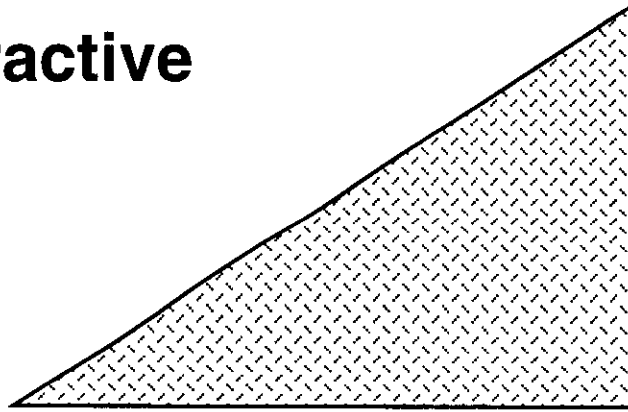
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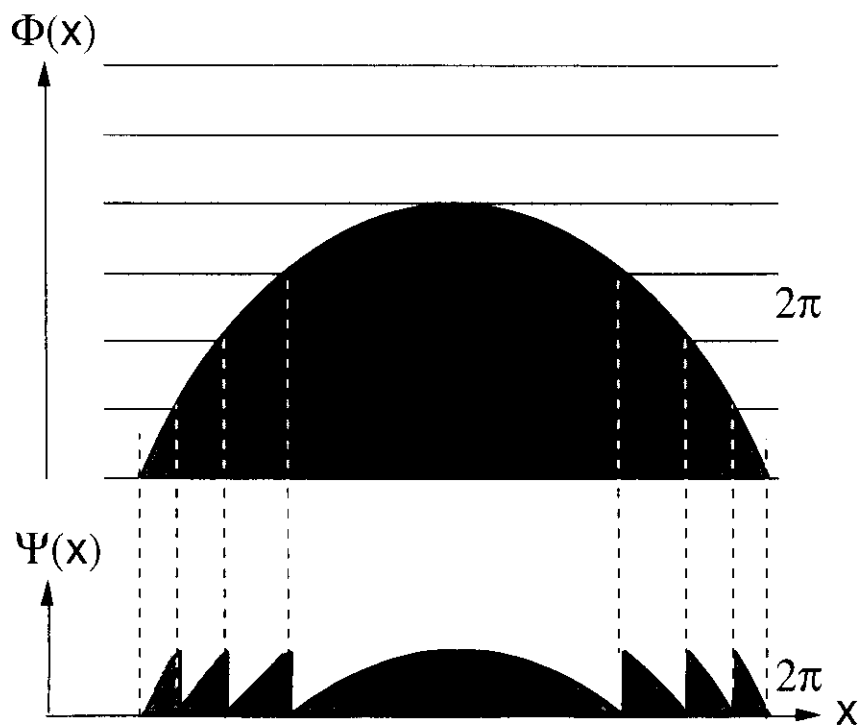
refractive



diffractive



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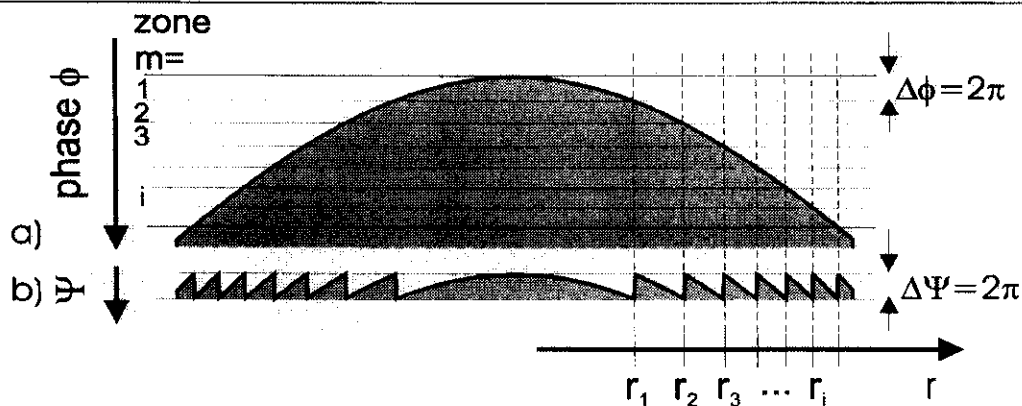
Design of continuous-relief DOEs

- I) Calculate DOE phase function ϕ
analytical, custom or commercial (ray-trace) program.

$$\phi_{in}(x, y) + \phi(x, y) = \phi_{out}(x, y)$$



- II) Wrap phase

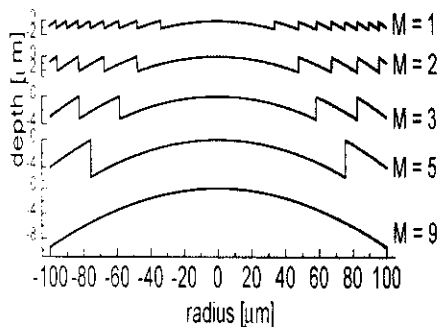


- III) Transform wrapped phase into surface relief

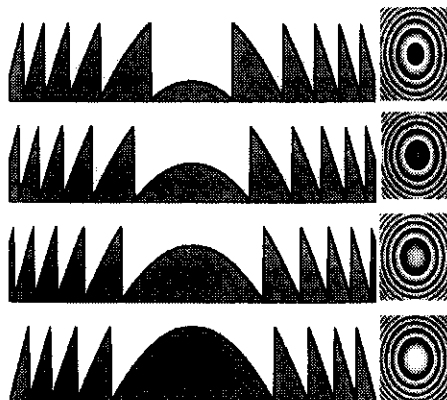
Design freedoms

$$\Psi(r) = [\phi(r) + \varphi_m + \varphi_0] \bmod (M_m 2\pi) - \varphi_m$$

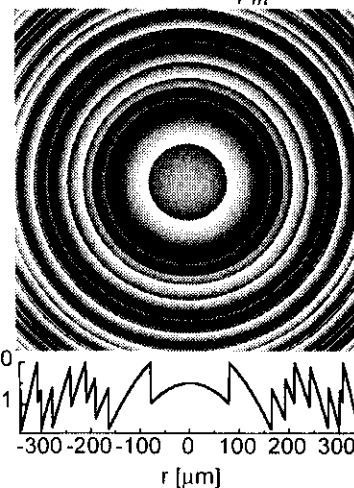
Phase-matching number M_m



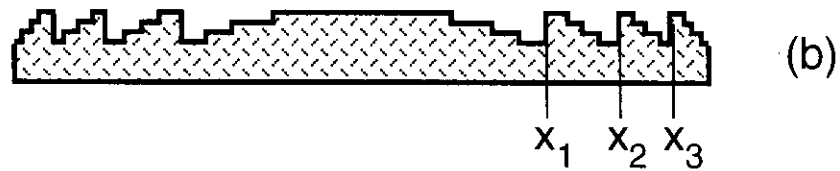
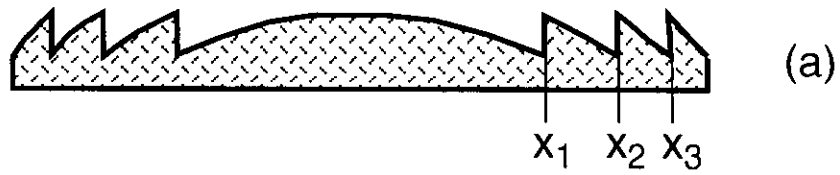
Phase offset φ_0



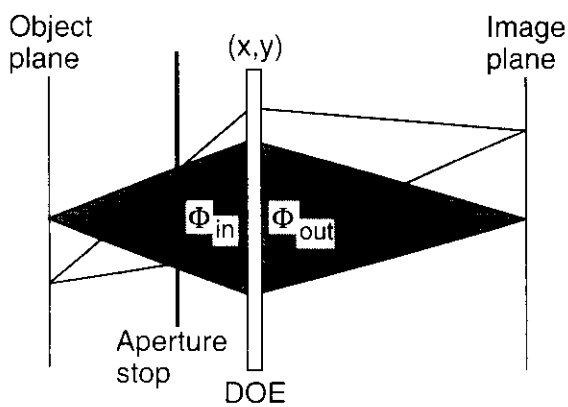
Zone position and size φ_m



Binary and continuous-relief DOEs

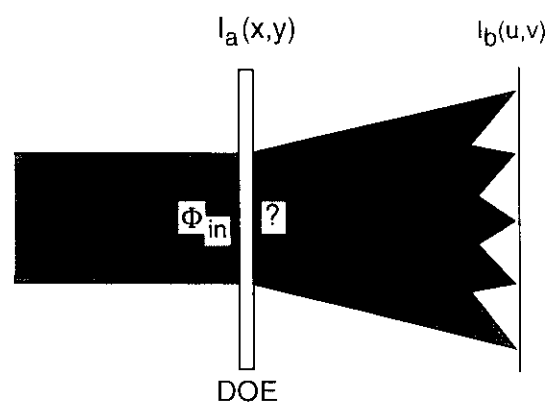


Optimum design



(a)

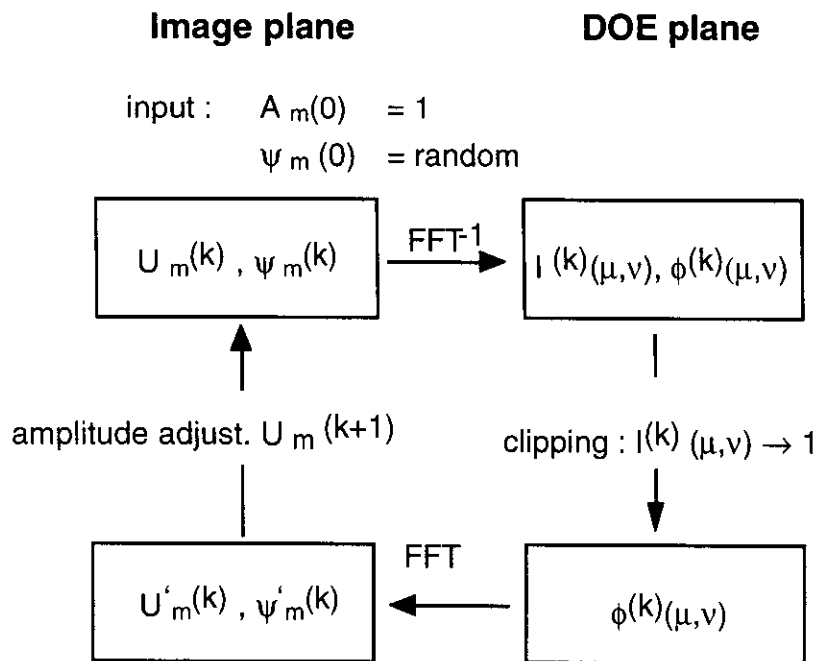
(a) Imaging



(b)

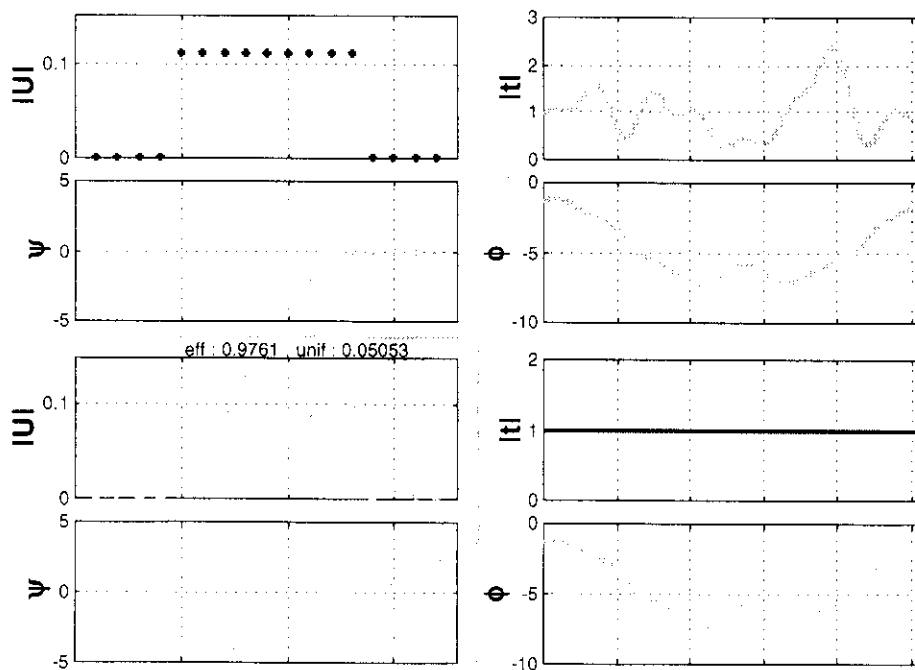
(b) Beam-shaping

Iterative Fourier algorithm (IFTA)



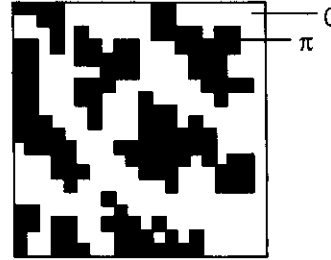
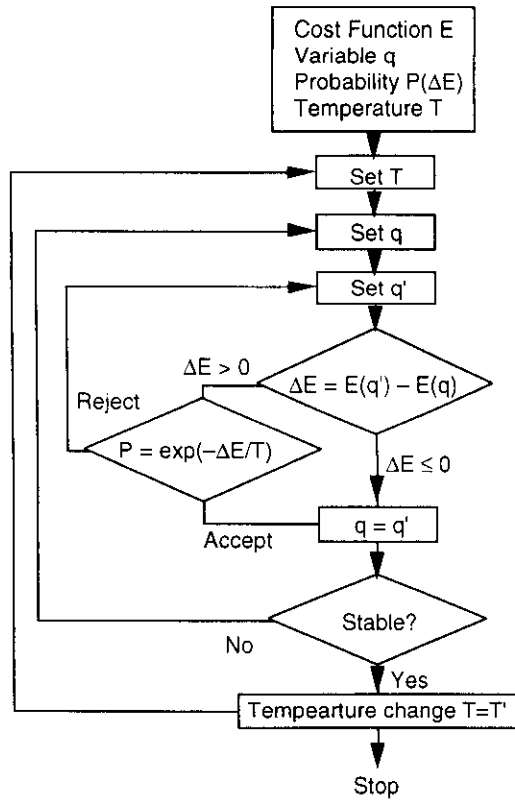
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Example: fan-out 9x1



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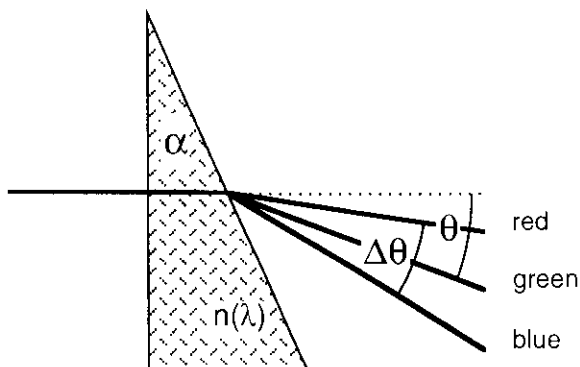
Simulated annealing



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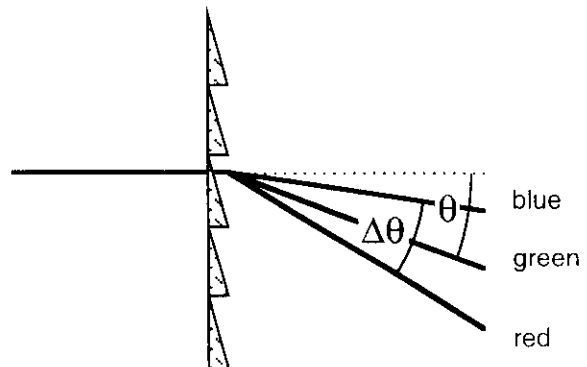
Dispersion

Refraction



$$v_r = \frac{\theta}{\Delta\theta} = \frac{n_d - 1}{n_F - n_C}$$

Diffraction



$$v_r = \frac{\theta}{\Delta\theta} = \frac{\lambda_d - 1}{\lambda_F - \lambda_C}$$

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Dispersion

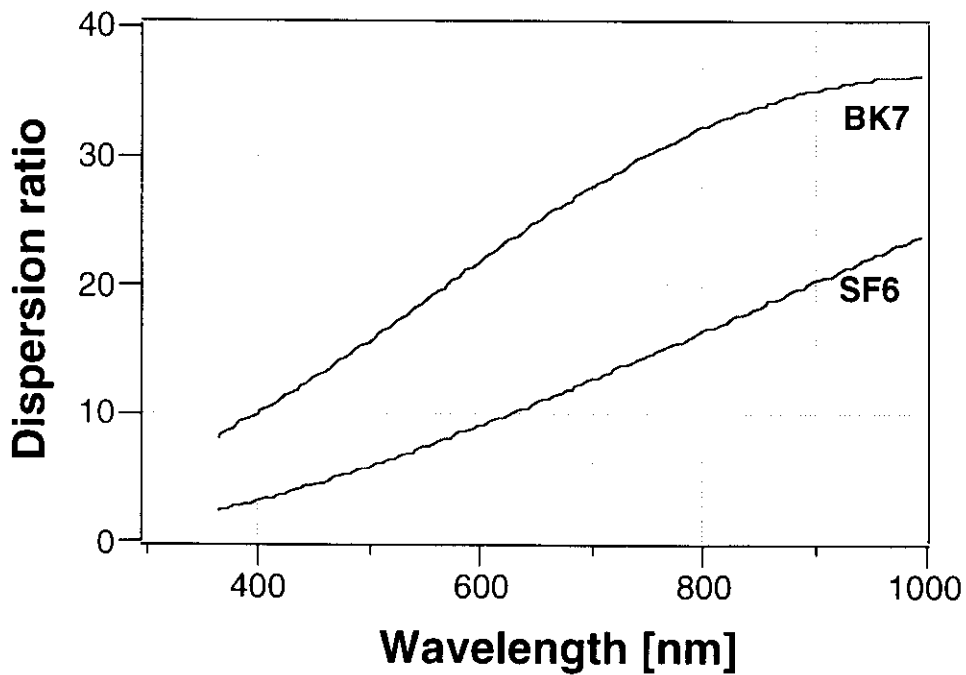
	Refractive	Diffraction
Abbe number:	$v_r = \frac{n(\lambda_1) - 1}{n(\lambda_2) - n(\lambda_3)}$	$v_d = \frac{\lambda_1}{\lambda_2 - \lambda_3}$
$\lambda_1 = 587.6 \text{ nm}$ $\lambda_2 = 486.1 \text{ nm}$ $\lambda_3 = 656.3 \text{ nm}$	$v_r = 80 \text{ to } 20$	$v_d = -3.45$

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Dispersion ratio $D_r = v_{\text{refractive}} / v_{\text{diffraction}}$

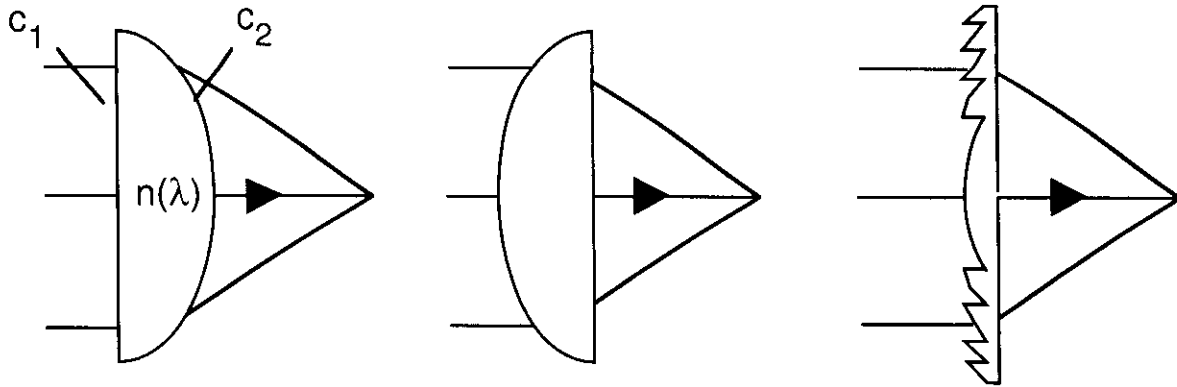


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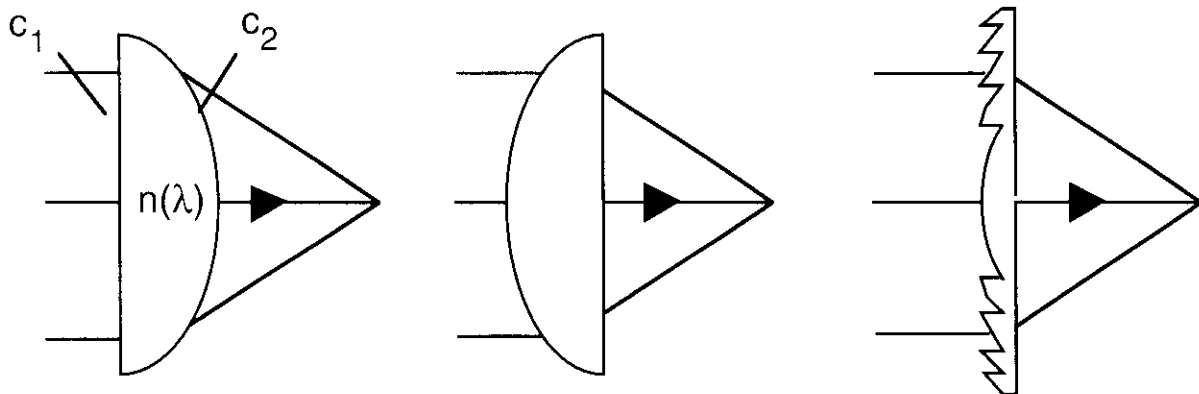
Paraxial properties of lenses



$$f_r(\lambda) = \frac{1}{n(\lambda) - 1} \frac{1}{c_1 - c_2} \quad f_d(\lambda) = f_0 \frac{\lambda_0}{\lambda}$$

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Spherical aberration $S_i = (NA)^4 f C_i$



$$C_a = \frac{n^2}{(n-1)^2}$$

$$C_b = \frac{n^3 - 2n^2 + 2}{n(n-1)^2}$$

$$C_c = 1 - \left(\frac{l_0}{l}\right)^2$$

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Airy disk radius

Refractive	Diffractive
$r(\lambda) = 1.22 \frac{\lambda f}{D}$	$r(\lambda) = 1.22 \frac{\lambda_0 f_0}{D} \approx \text{const}$

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Diffractive elements

- Arbitrary shape
- Accurate focal length
- High functionality
- High dispersion (<0)
- Problems:
 - low NA (< 0.2)
 - diffraction efficiency (80% - 95%)
 - stray-light

Refractive elements

- Spherical and cylindrical shape
- High NA (> 0.1)
- Low dispersion (>0)
- High efficiency
- Low stray-light
- Problems:
 - fill factor
 - arbitrary shapes

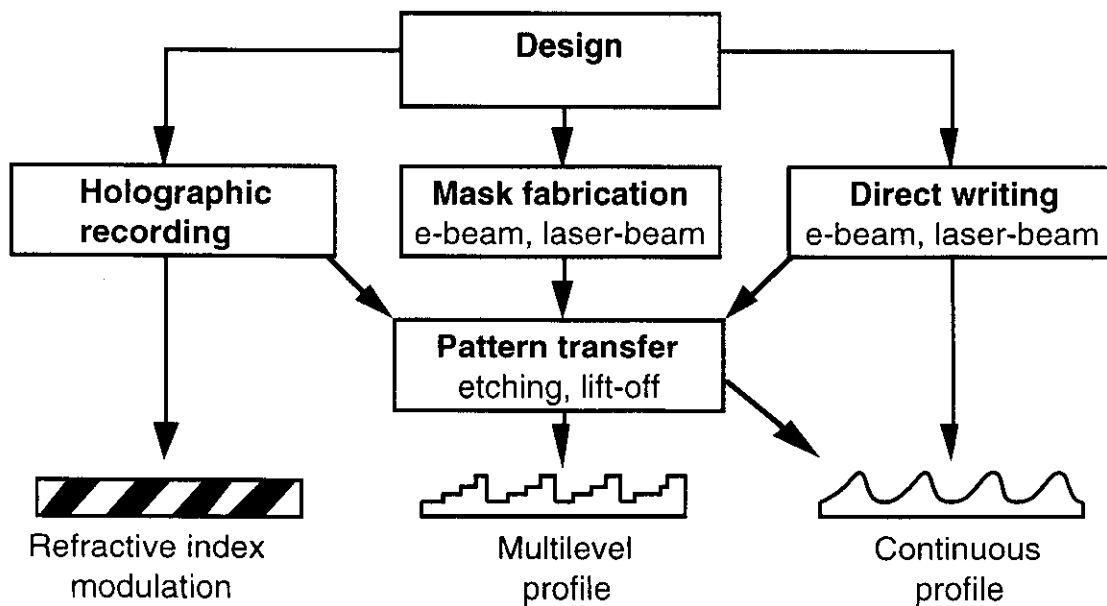
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Fabrication of micro-optical elements

- Fabrication of diffractive optical elements
- Gray-tone lithography
- Melting resist technology
- Profile shaping by RIE

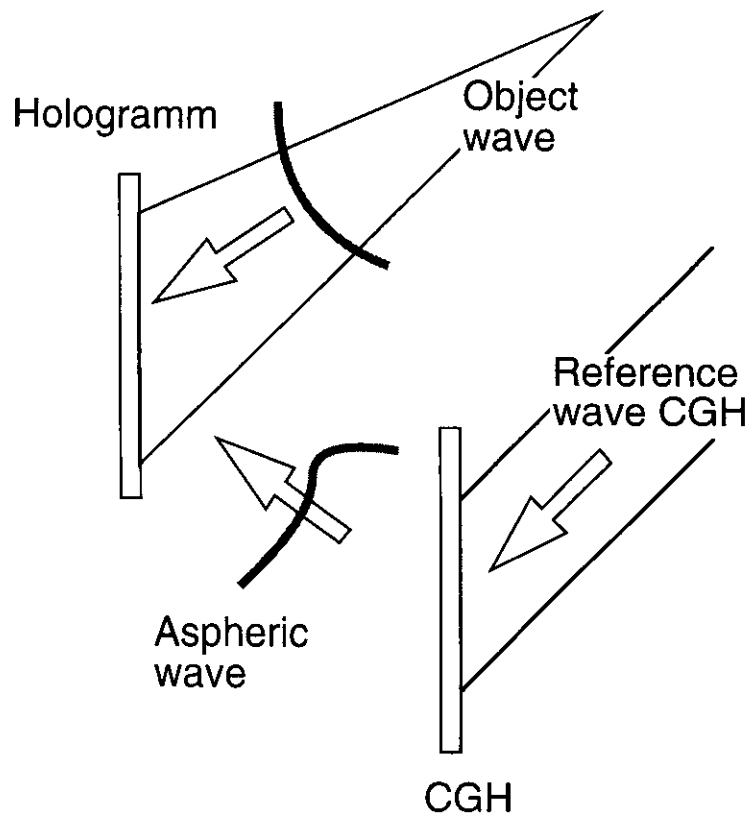
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Fabrication methods



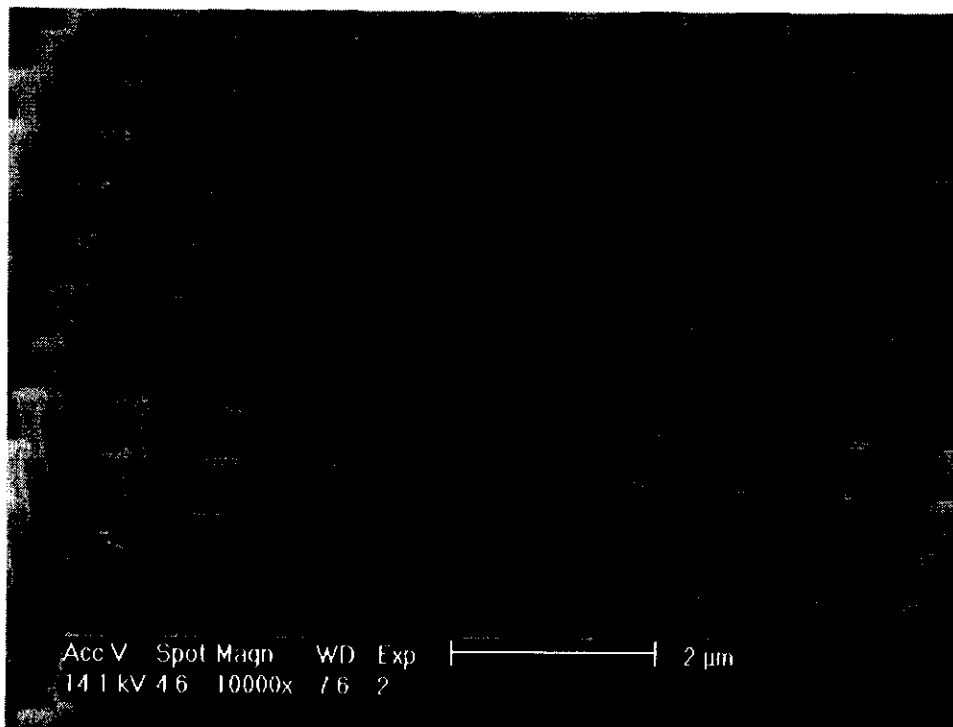
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Holographic recording

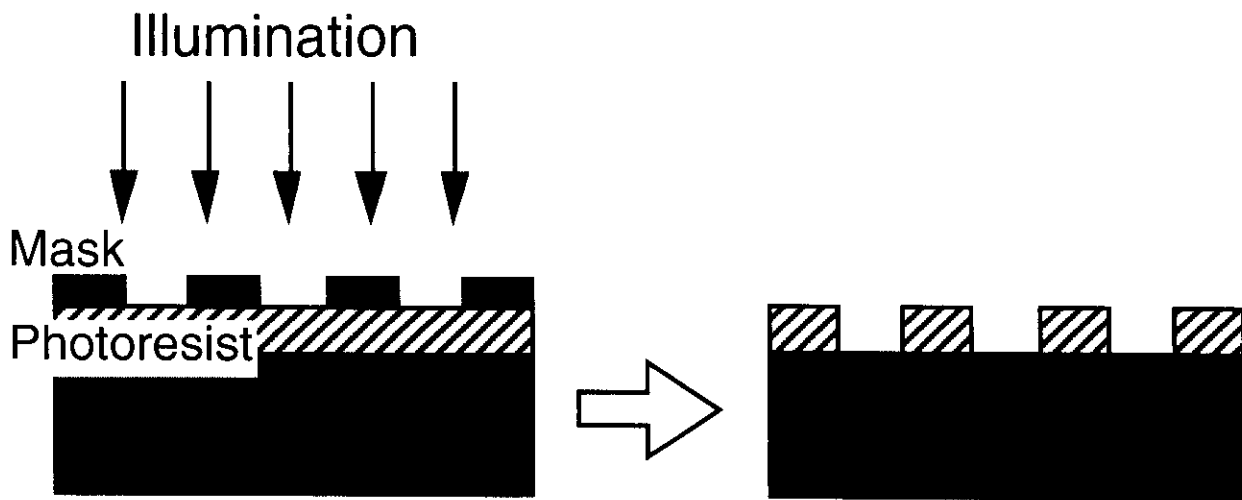


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Crossed gratings ($\Lambda = 1 \mu\text{m}$)



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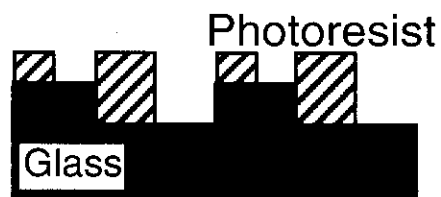
Mask level 1



Etch 1 ↓



Mask level 2

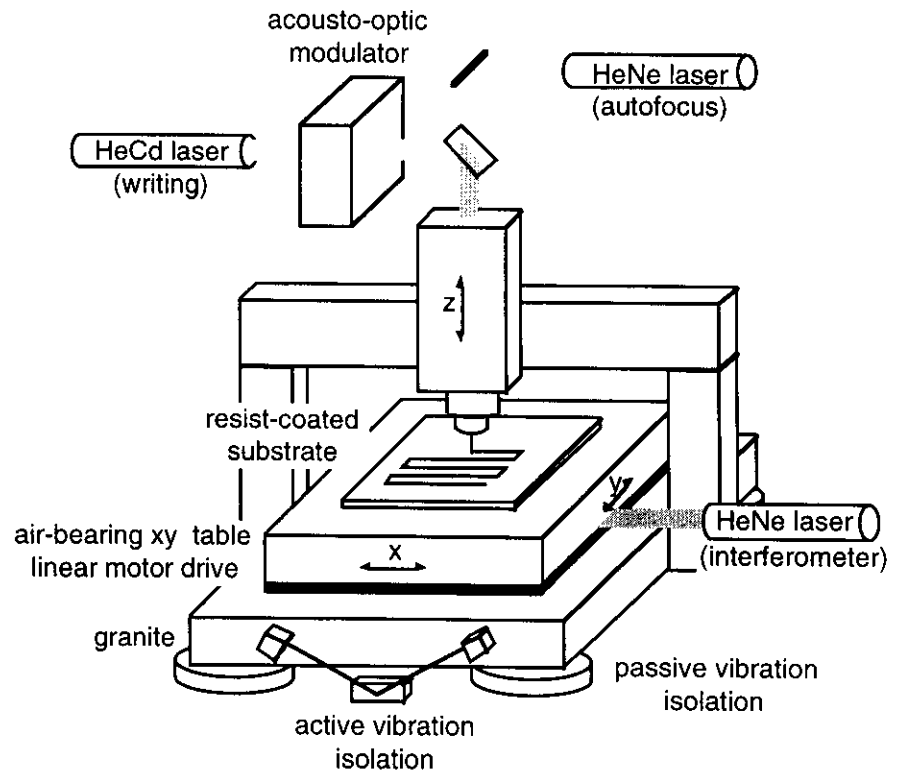


Etch 2 ↓



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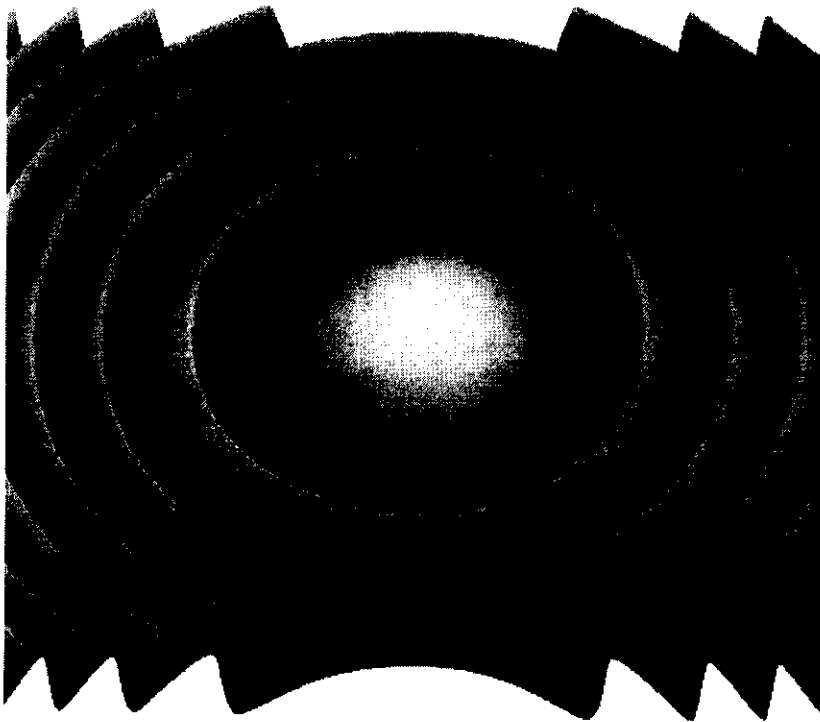
Laser-beam writing



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Diffractive optical element (DOE)

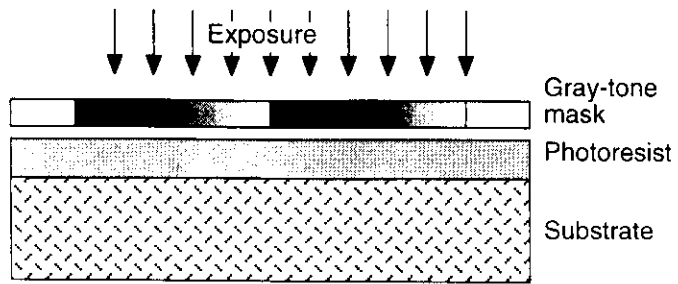


Direct laser writing
at CSEM Zurich

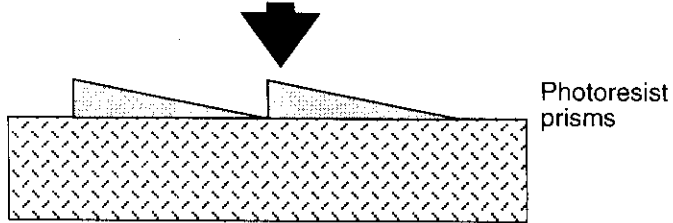
(M. T. Gale, M.
Rossi)

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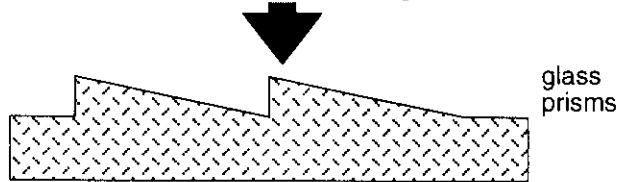
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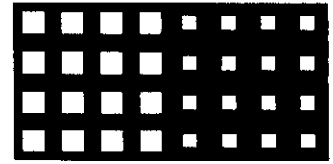
Development



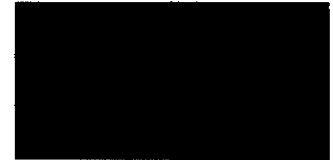
Reactive ion etching



Gray-tone mask



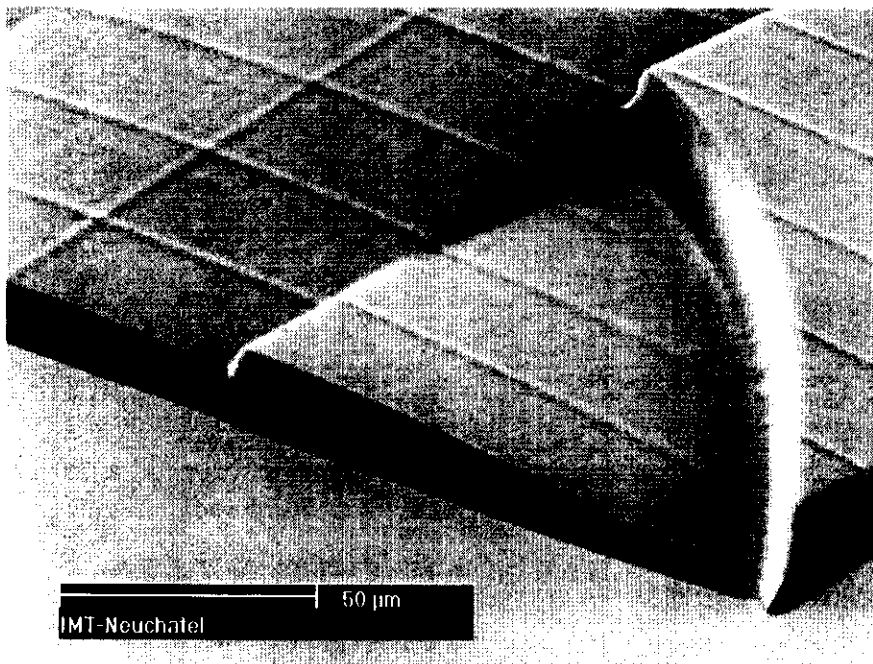
fill-factor



HEBS-Glass

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Gray-tone technology: structure in photoresist

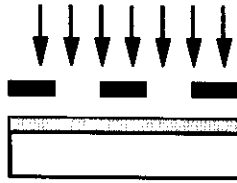


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MELTING RESIST TECHNOLOGY

Fabrication of microlens arrays



light
mask
resist
substrate

Photolithography



resist cylinders
substrate

Resist cylinders



micro lenses
substrate

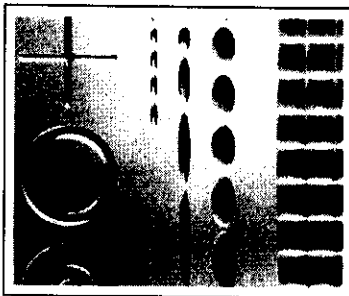
Melting (~150°C)



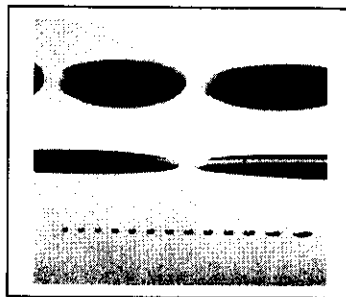
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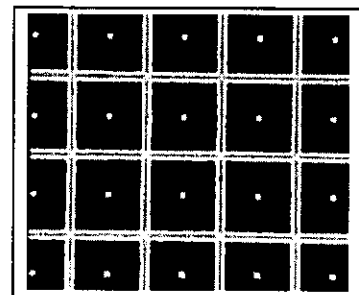
Melting resist microlenses



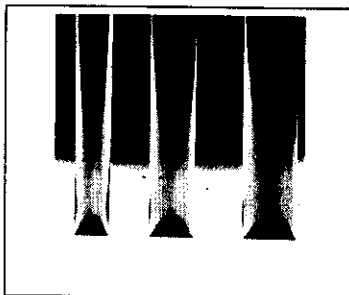
Non-spherical lenses



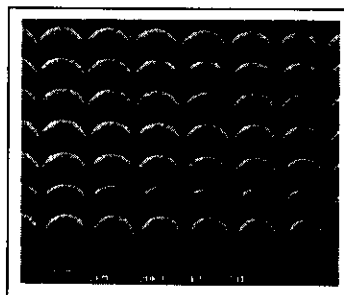
Elliptical lenses for off-axis imaging



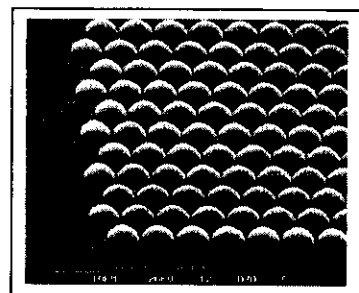
Square lenses



Cylindrical lenses



close packaging (0.2µm gap)



5µm lens diameter

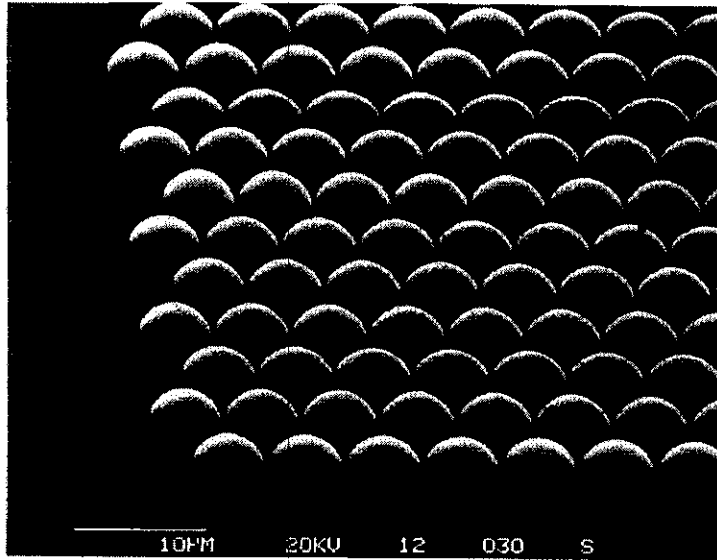


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MELTING RESIST MICROLENSES

IMT Neuchâtel - IBM ZRL - SUSS KG



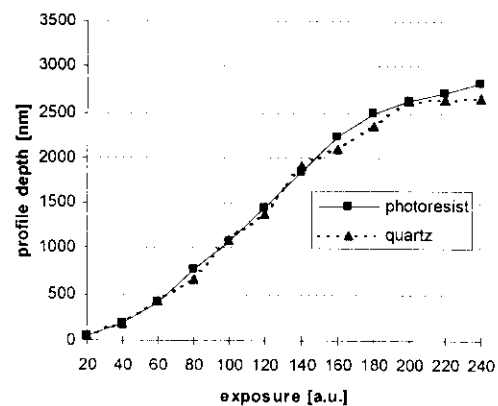
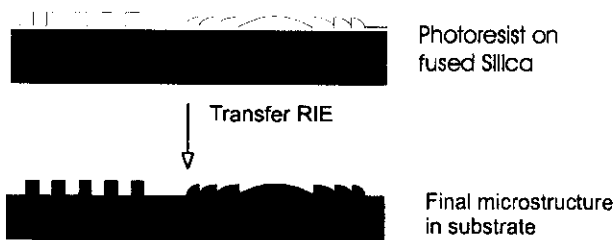
$\varnothing = 5\mu\text{m}^*$
1µm gap

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Transfer of laser beam written structures

(In cooperation with CSEM, Zürich, Switzerland)



- Transfer diffractive lenses with continuous-surface relief profiles of up to 3 µm depth
- 1:1 selectivity transfer to maintain the elements dimensions
- Possibility to correct depth errors of the photoresist structure
- Depth variations of less than 5 % for depths of 0 - 3 µm

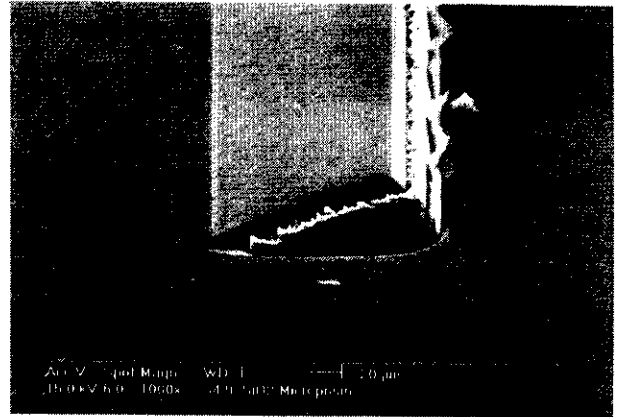
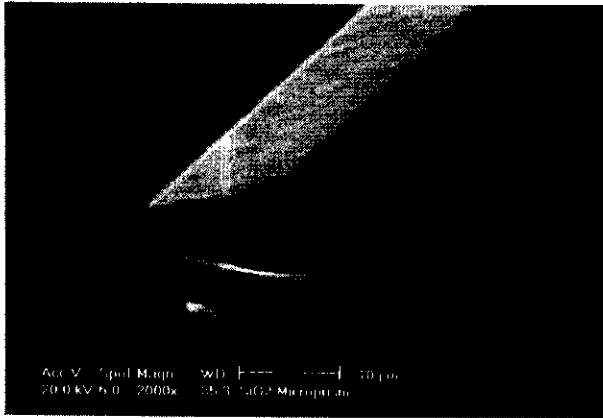
10/02/00


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Fused silica microprisms

(In cooperation with Friedrich Schiller University, Jena, Germany)

- SiO₂ microprisms realized by dry etching of photoresist structures realized by using graytone masks (HEBS glass).



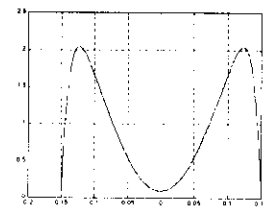
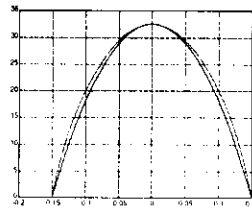
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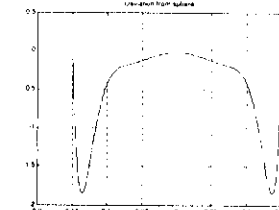
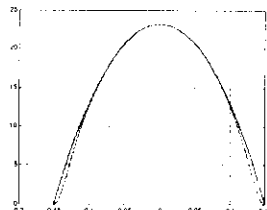
Profile shaping and low selectivity etching

- Shape modification of micro-optical elements during the transfer process
 - Correction of eventual fabrication errors of photoresist master element
 - Dynamic of selectivity for shape correction from 0.8:1 to 1.2:1
- Low selectivity etching: e.g. height 30 μm (photoresist) ⇒ 3 μm (fused silica).

Photoresist refractive microlens
 Diameter 300 μm, height 31.5 μm,
 max. deviation from sphere + 2 μm



Fused silica refractive microlens
 Diameter 300 μm, height 23 μm,
 max. deviation from sphere -1.8 μm



Profile measured with Mach-Zehnder interferometer

Deviation from perfect sphere

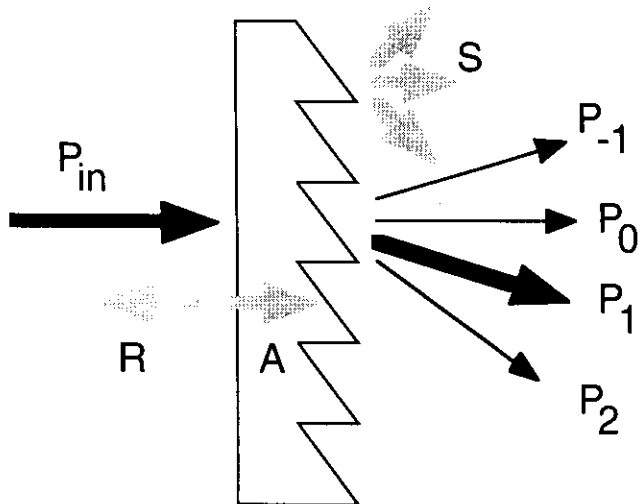
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MICROLENS ARRAYS

- Melting resist technology
- Refractive plano-convex microlenses
- 2 μm to 5 mm diameter possible
- Photoresist: $< f/5$, Quartz: $< f/30$
- Diffraction limited resolution
- Replication techniques
- RIE transfer in fused silica

Diffraction efficiency η



$$\eta = \frac{P_1}{\sum P_m}$$

$$\eta_{overall} = \frac{P_1}{P_{in}}$$

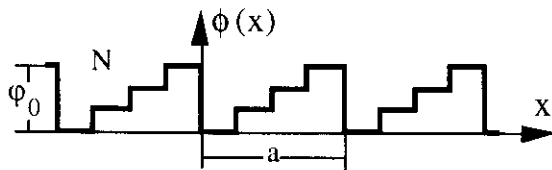
R: reflection
A: absorption
S: scattering

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Diffraction efficiency (scalar theory, no losses)



blazed grating: $\phi_0 = 2\pi$,

$$|A_n| = \frac{1}{N} \operatorname{sinc}\left(\frac{n}{N}\right) \frac{\sin\left[\pi\left(\frac{n-1}{N}\right)\right]}{\sin\left[\pi\left(\frac{n-1}{N}\right)\right]}$$

$$|A_1|^2 = \left[\frac{N}{\pi} \sin\left(\frac{\pi}{N}\right) \right]^2$$

N: number of phase levels
n: diffraction order

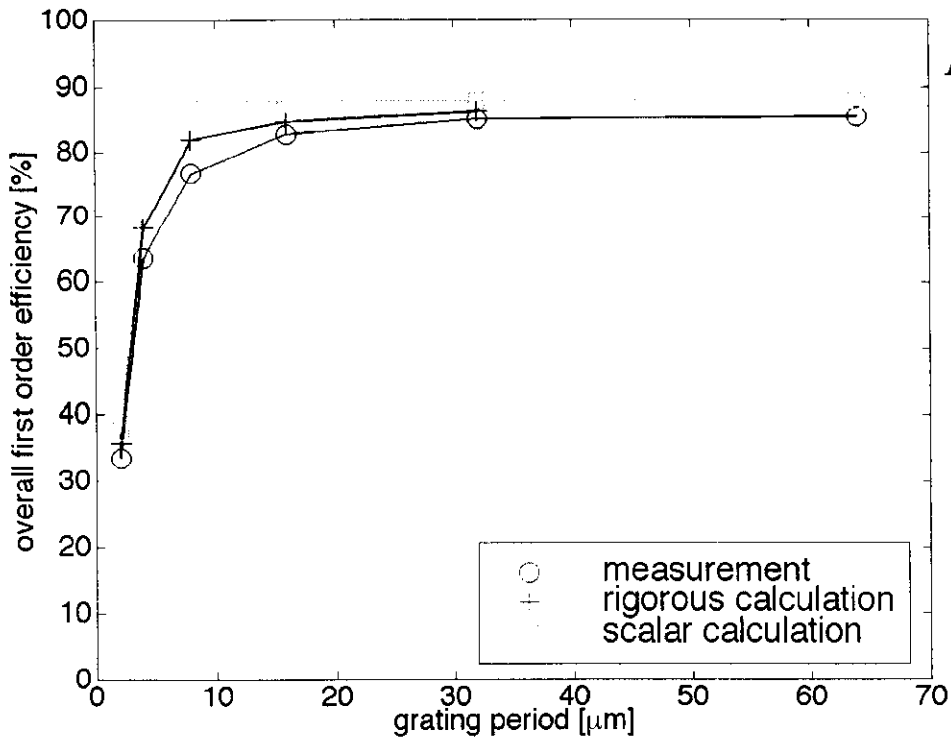
N =	2	4	8	16
$ A_1 ^2 =$	40.5%	81,1%	95,0%	98,7%

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Diffr. efficiency: theory - experiment



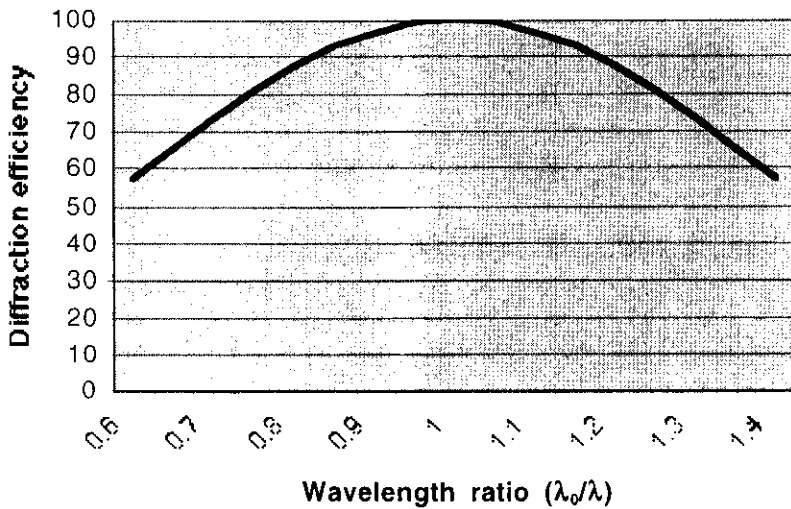
A. Schilling

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Diffraction efficiency versus wavelength



$$\eta(\lambda) = \left(\frac{\sin\left\{ \pi \left[\left(\frac{\lambda}{\lambda_0} \right) - m \right] \right\}}{\pi \left[\left(\frac{\lambda}{\lambda_0} \right) - m \right]} \right)^2$$

Swanson, 1989

$$\eta_{poly} = \frac{\int_{\lambda_{min}}^{\lambda_{max}} \eta(\lambda) d\lambda}{\lambda_{max} - \lambda_{min}}$$

Buralli and Morris 1992

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Aperture modulated diffusers (AMDs)

H. P. Herzig

Institute of Microtechnology University of Neuchâtel

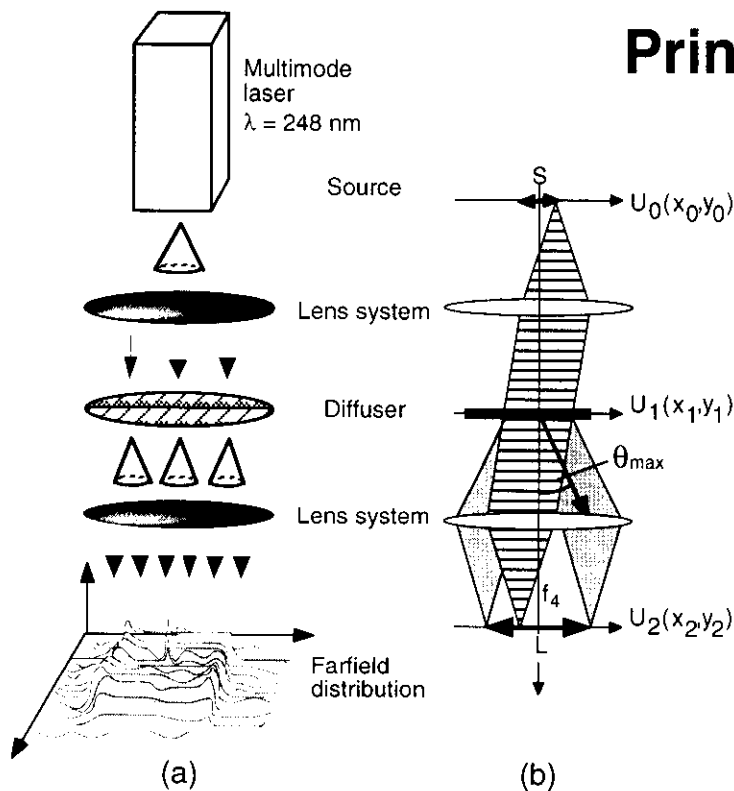
<http://www-imt.unine.ch/>

hanspeter.herzig@imt.unine.ch



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Principle of AMDs



Aperture shape: $a(x_1, y_1)$

Transmission function:

$$t(x_1, y_1) = a(x_1, y_1) \exp[i\Phi(x_1, y_1)]$$

Coherent:

$$\begin{aligned} I_2(x_2, y_2) &= |U_2(x_2, y_2)|^2 = |\text{FT}\{U_1(x_1, y_1)\}|^2 \\ &= |\text{FT}\{\text{FT}^{-1}\{U_0(x_0, y_0)\} \cdot t(x_1, y_1)\}|^2 \\ &= |U_0(x_0, y_0) \otimes \text{FT}\{t(x_1, y_1)\}|^2 \end{aligned}$$

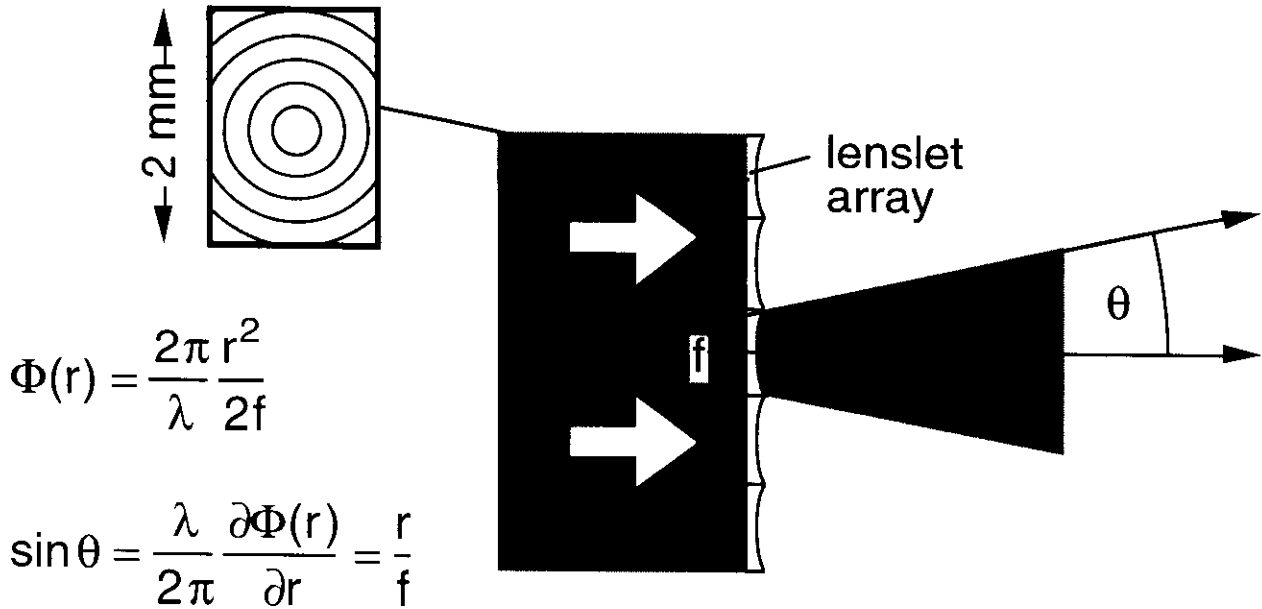
Incoherent

$$I_2(x_2, y_2) = |U_0(x_0, y_0)|^2 \otimes |\text{FT}\{t(x_1, y_1)\}|^2$$



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Design



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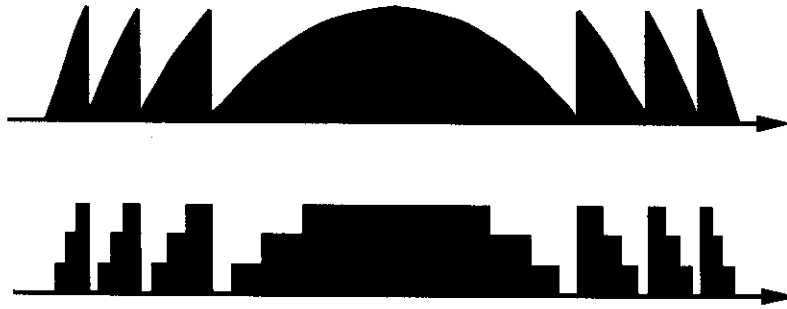
Specification of diffuser

- Flat-top with rectangular shape
(e.g. 7 deg x 3 deg)
- Space invariant design
- Deflection angle of 7 deg at $\lambda = 248$ nm
 \Rightarrow grating period $\Lambda = 2 \mu\text{m}$ (mfs = $1 \mu\text{m}$)
- High diffraction efficiency $> 80 \%$
- Fabrication of elements in quartz

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Diffraction efficiency

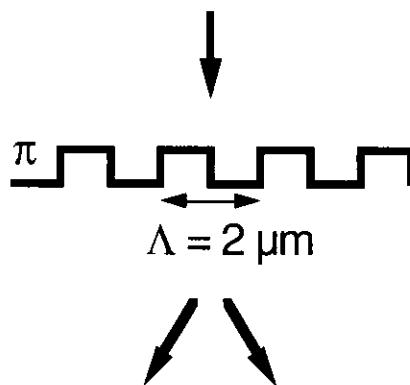


Diffraction efficiency:	2 phase levels	40.5 %
	4	81 %
	8	95 %

Problem: Fabrication of a lens with smallest feature size of 1 μm

- Possible solutions:
- Binary lens
 - 8-4-2 level lens
 - Continuous-relief lens

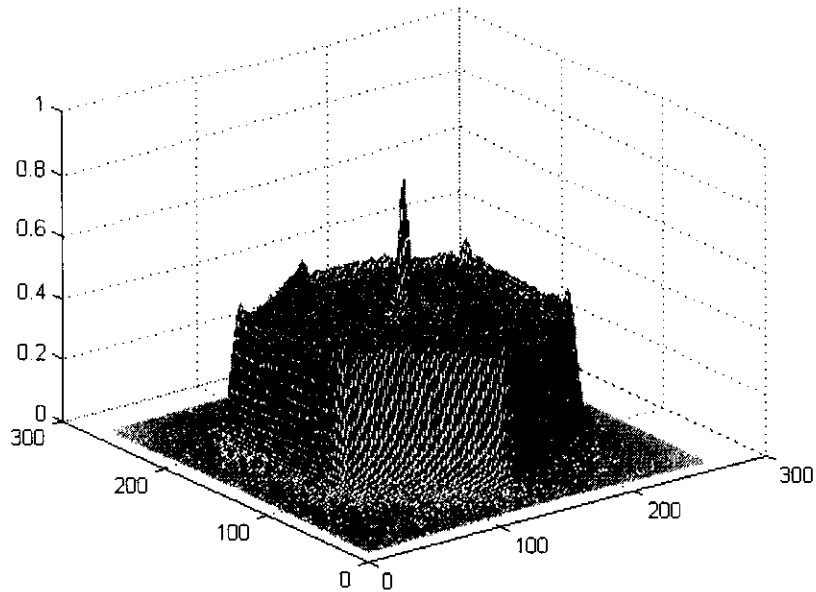
Diffraction efficiency of binary gratings



Binary lens $\eta = 40.5 \%$

Binary diffuser $\eta \geq 81.0 \%$

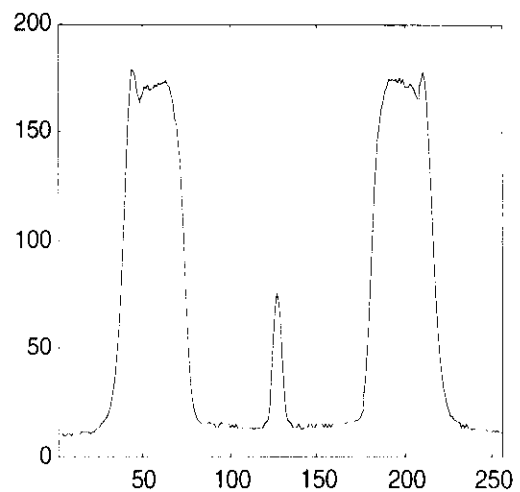
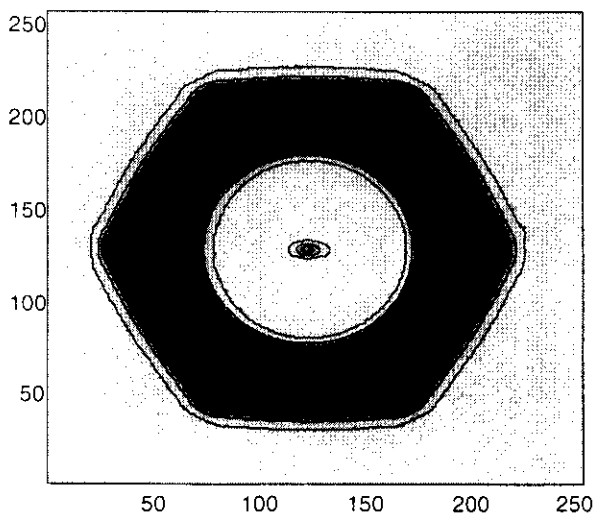
Far-field of a hexagonal diffuser



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Annular Diffuser



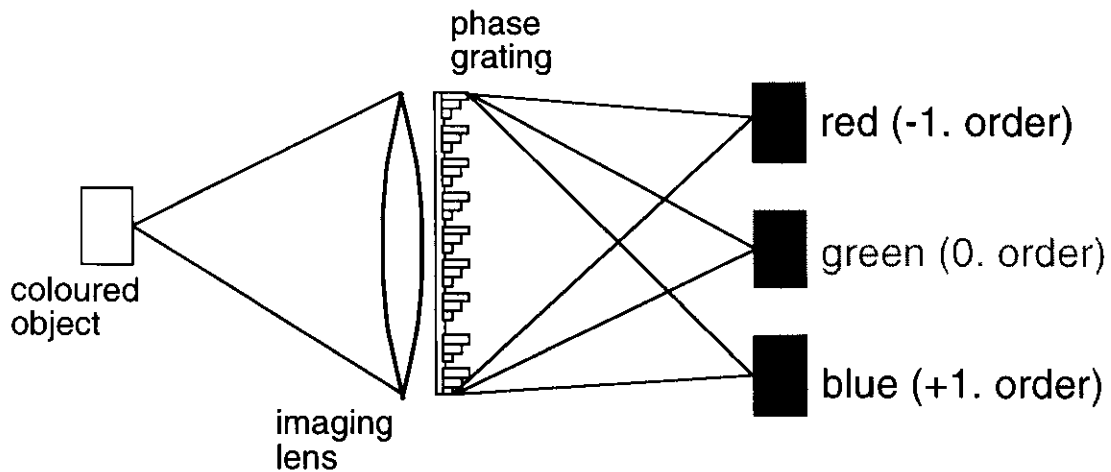
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Color fan-out: principle

A. Schilling

Color fan-out elements are special phase gratings which project the three color components blue, green, and red into the three central diffraction orders.



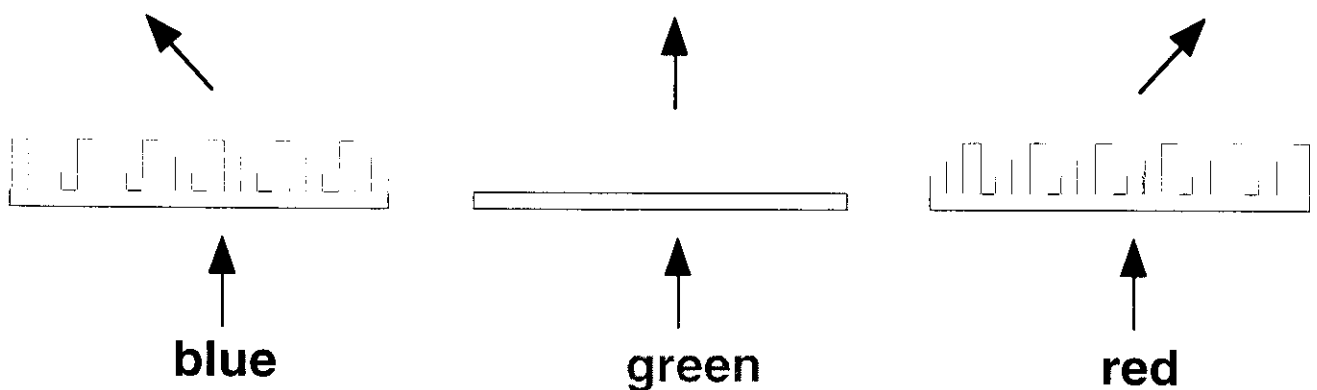
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Color fan-out: principle

Desired phase profiles of the diffraction gratings for the three color components:



Solution: overphasing of phase structures (deep phase gratings)

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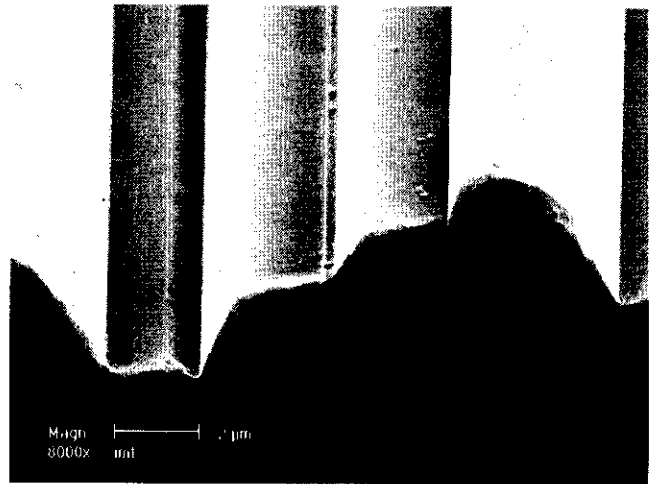
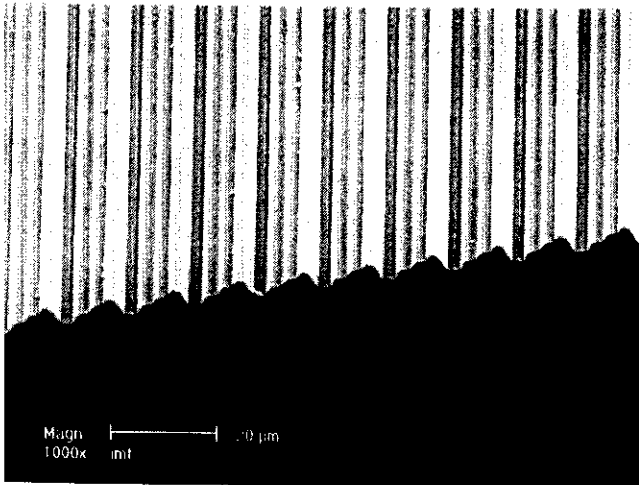
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Color fan-out elements: SEM images

Color fan-out elements etched in quartz:

- 12 μm grating period
- 3.3 μm profile depth



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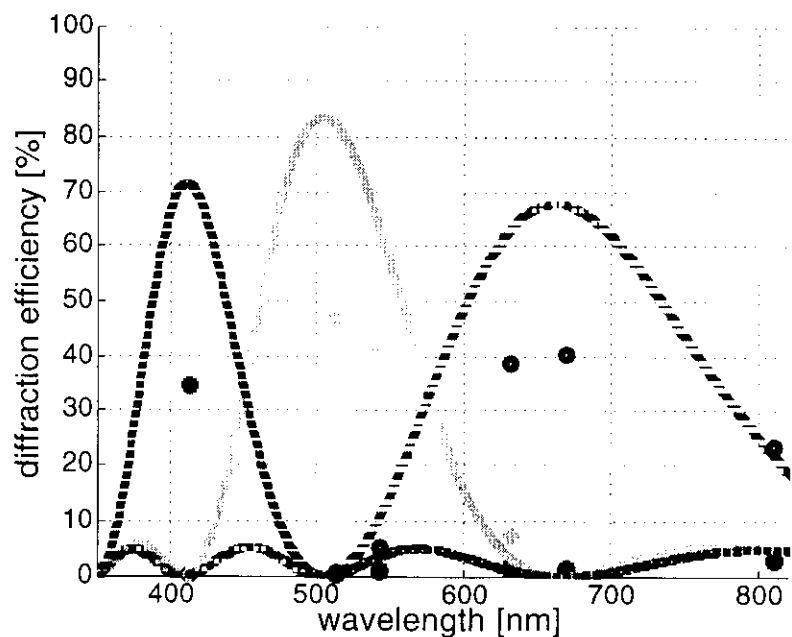
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Color fan-out elements: efficiencies

Characterization of color fan-out elements (quartz):

- 4 phase levels
- 16 μm grating period
- 3.3 μm profile depth

rigorous theory (lines) and measurement (markers)



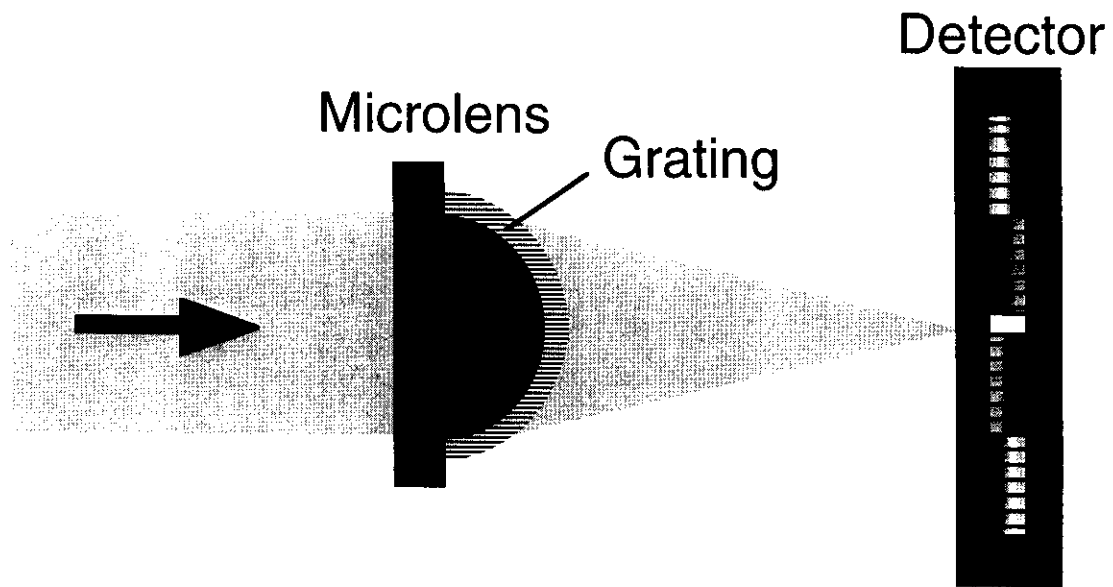
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Application: μ -spectrometer

S. Traut



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Holographic recording

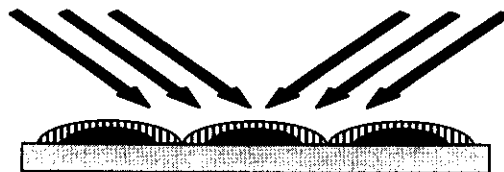
1) Fabrication of a microlens array



2) Photoresist coating of the array by spincoating



3) Holographic recording of the grating

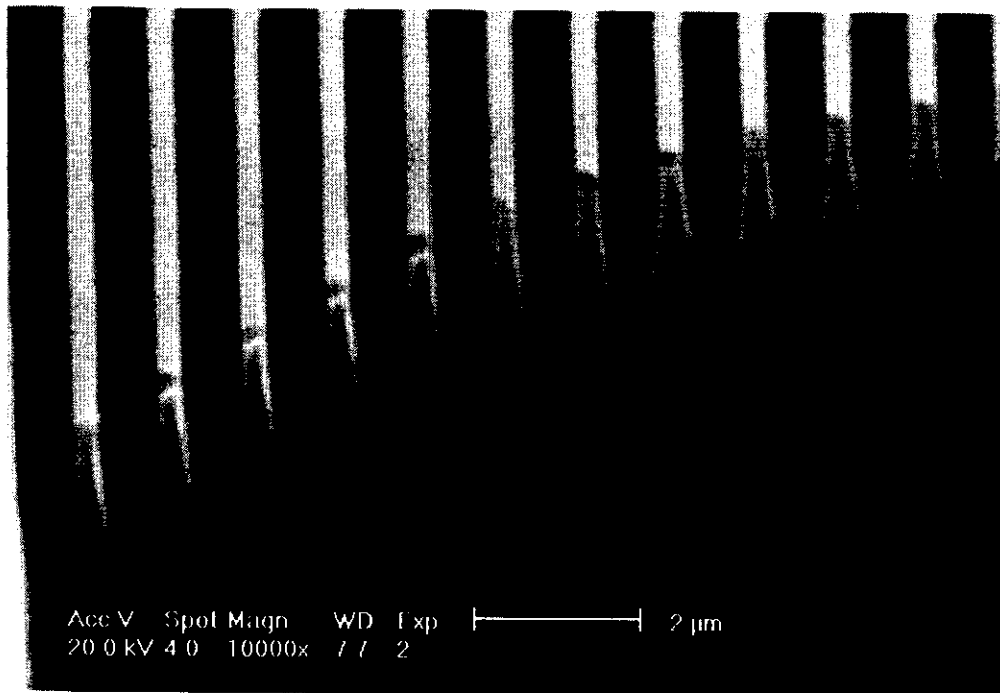


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Grating on top of a refractive microlens



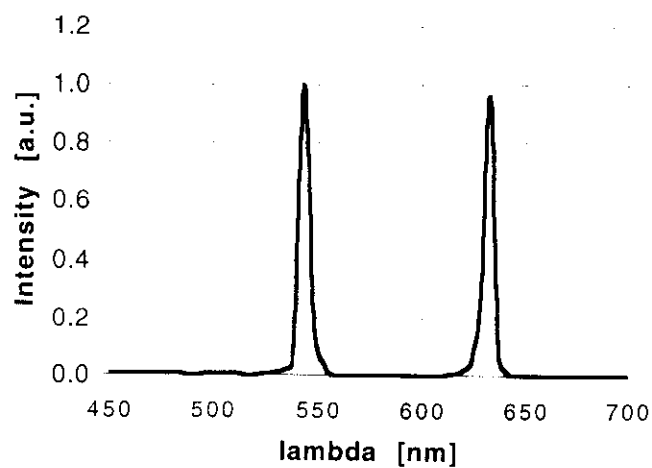
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Resolution

Resolution of μ -Spec610



<u>lens diameter</u>	<u>measured resolution</u>
350 μm	11 nm
610 μm	6 nm
990 μm	4 nm

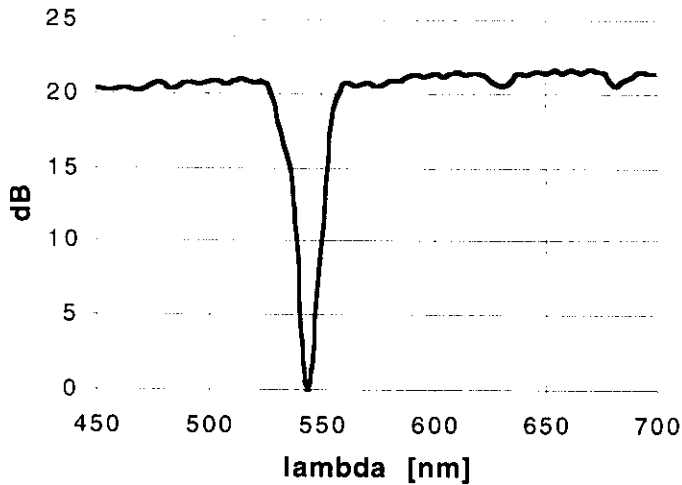
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Stray-light suppression

μ -Spec610 performance



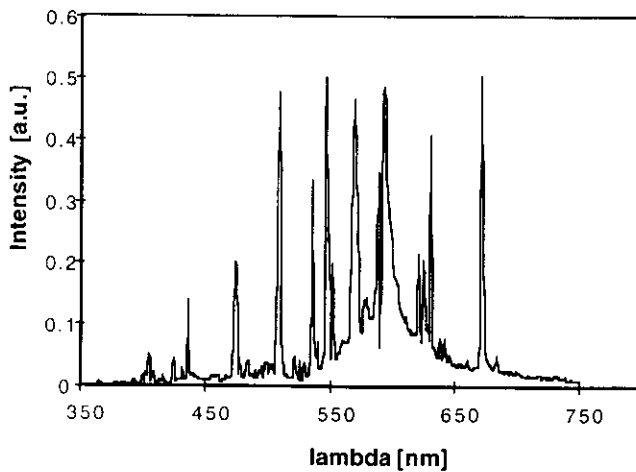
<u>lens diameter</u>	<u>measured damping</u>
350 μm	6-9 dB
610 μm	20-22 dB
990 μm	18-20 dB

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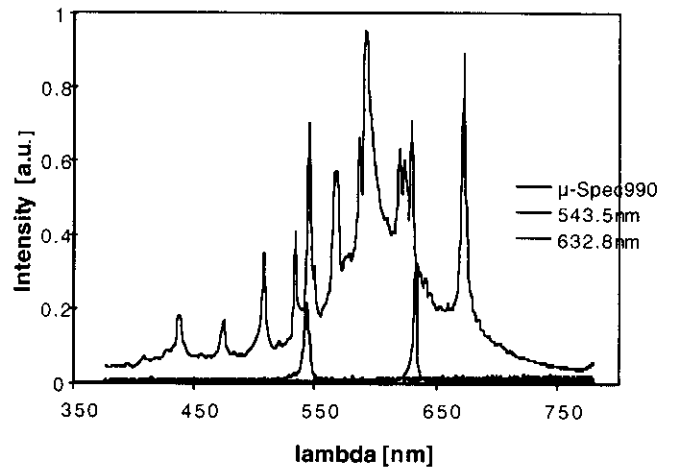
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Spectrum of a Xenon lamp

HR250 (1 nm resolution)



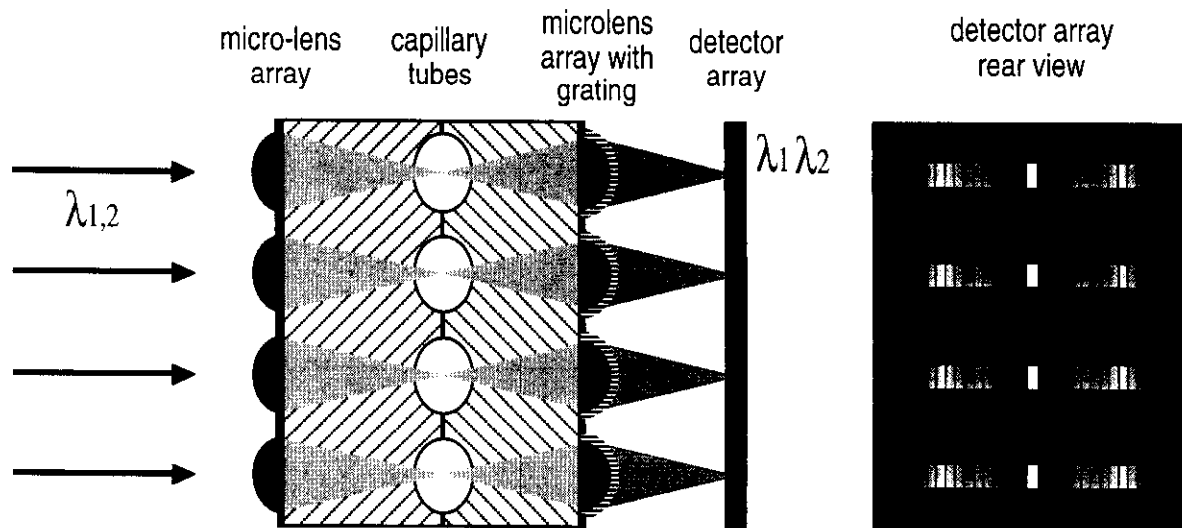
μ -Spec990



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Concept of a μ -Spec System



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Miniaturized Fourier Transform Spectrometers

Hans Peter Herzig and Omar Manzardo
 Institute of Microtechnology, University of Neuchâtel
 www-optics.unine.ch

Acknowledgments: C. Marxer, IMT-Uni NE
 H. Teichmann, CSEM Zurich

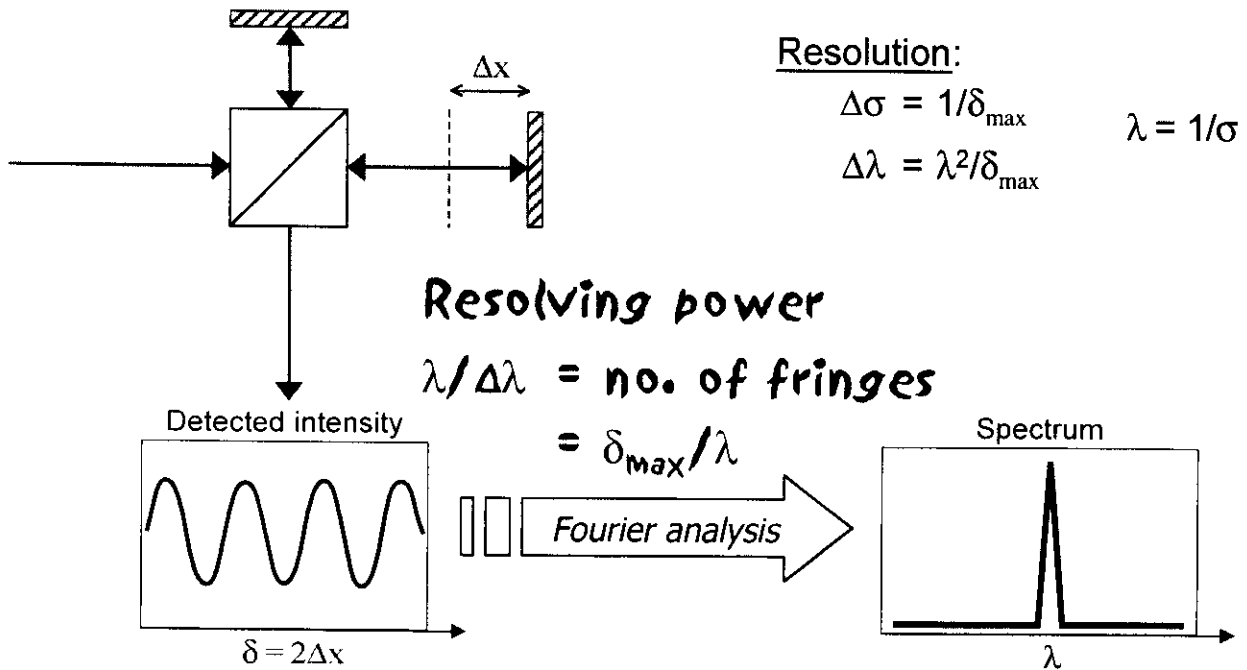


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Fourier Transform Spectroscopy

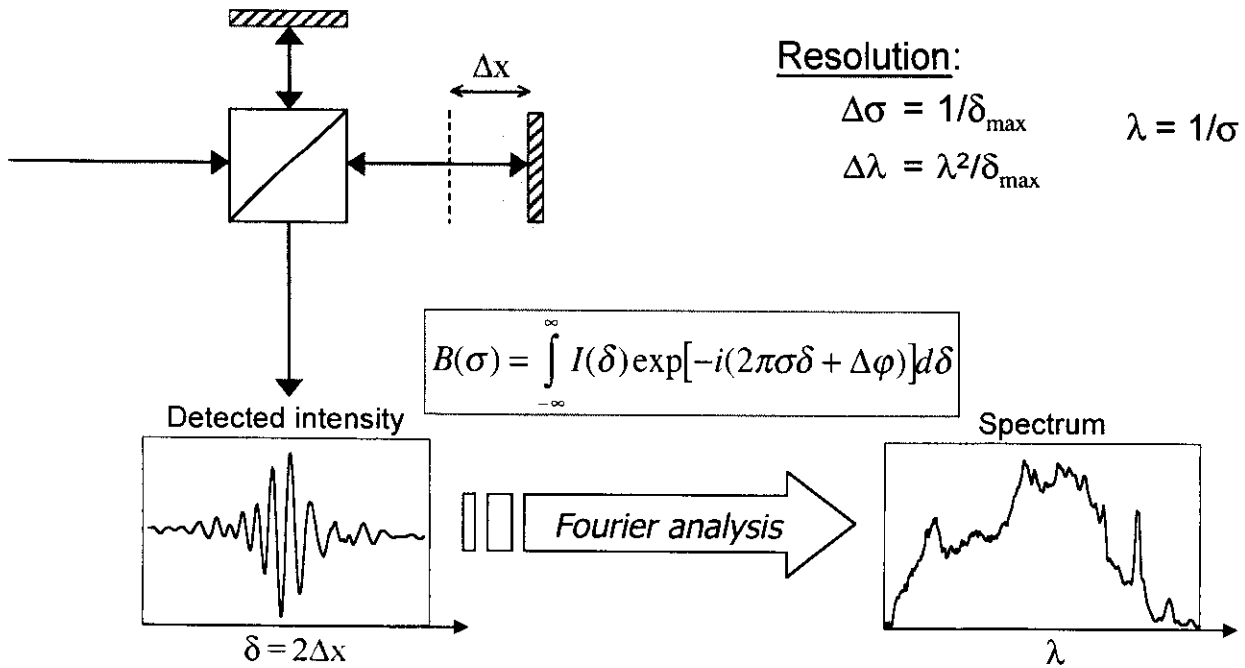


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Fourier Transform Spectroscopy

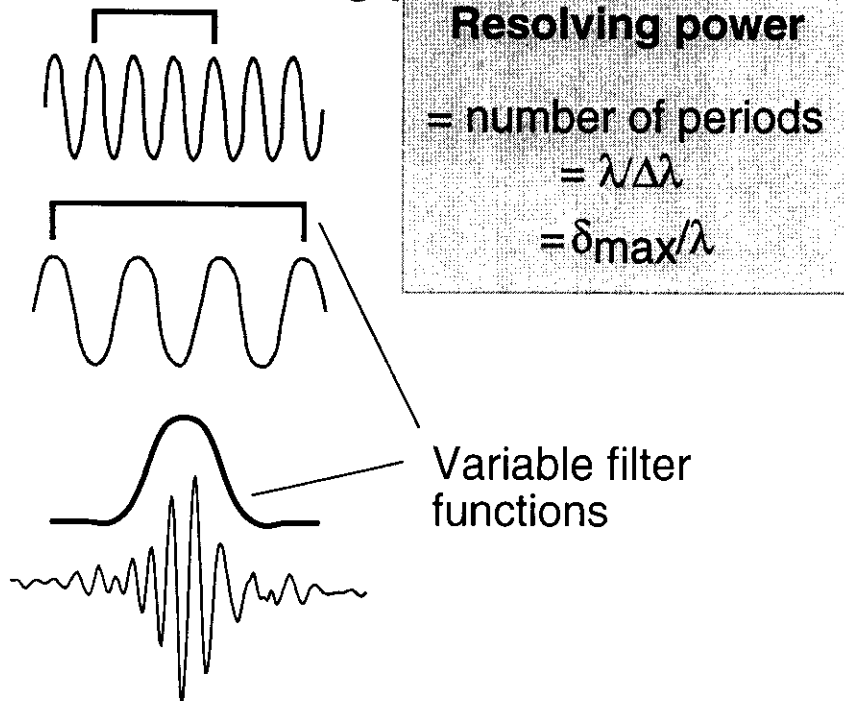


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Resolving power - filtering

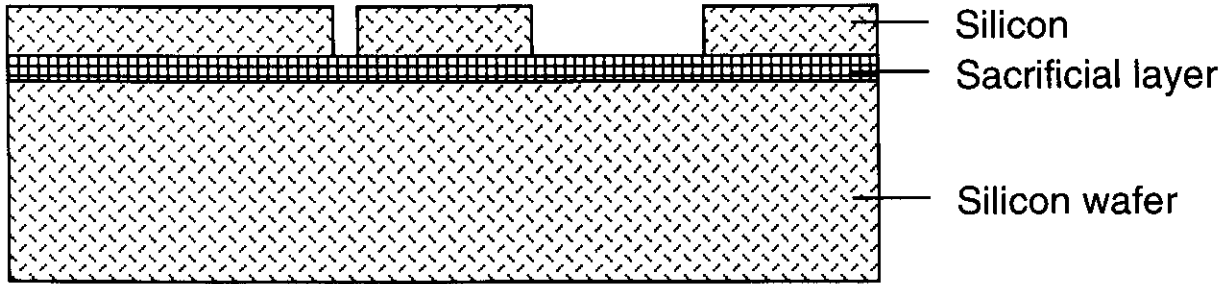


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Surface micromachining



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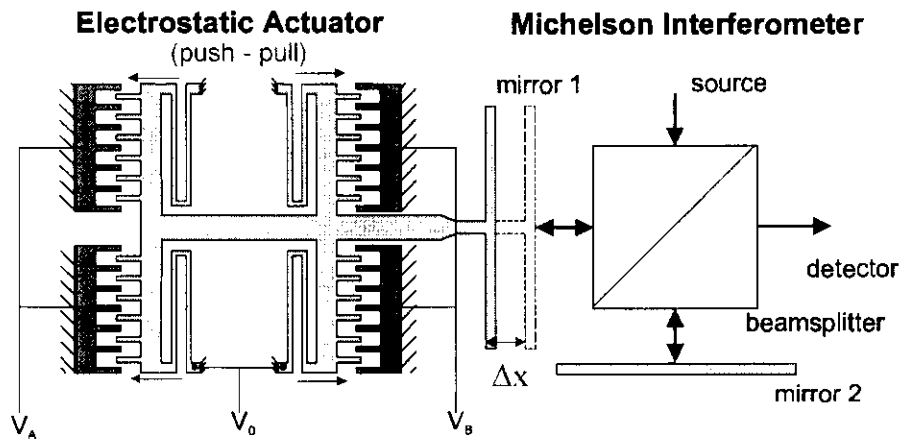
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Setup

2/1.1651 Displacement of the mirror

2/ Free analysis



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Actuator

Mirror (Al coated)

Electrostatic comb - V_A, V_0, n, h, g

Spring - k

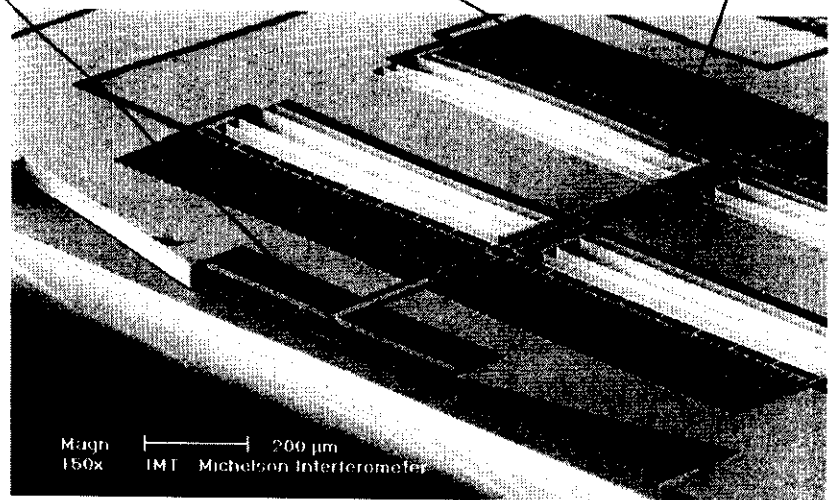
Mirror displacement

$$\Delta x = \frac{1}{k} \epsilon_0 n \frac{h}{g} 2V_A V_0$$



$$\Delta x_{\max} = 40 \mu\text{m}$$

$$\delta_{\max} = 80 \mu\text{m}$$

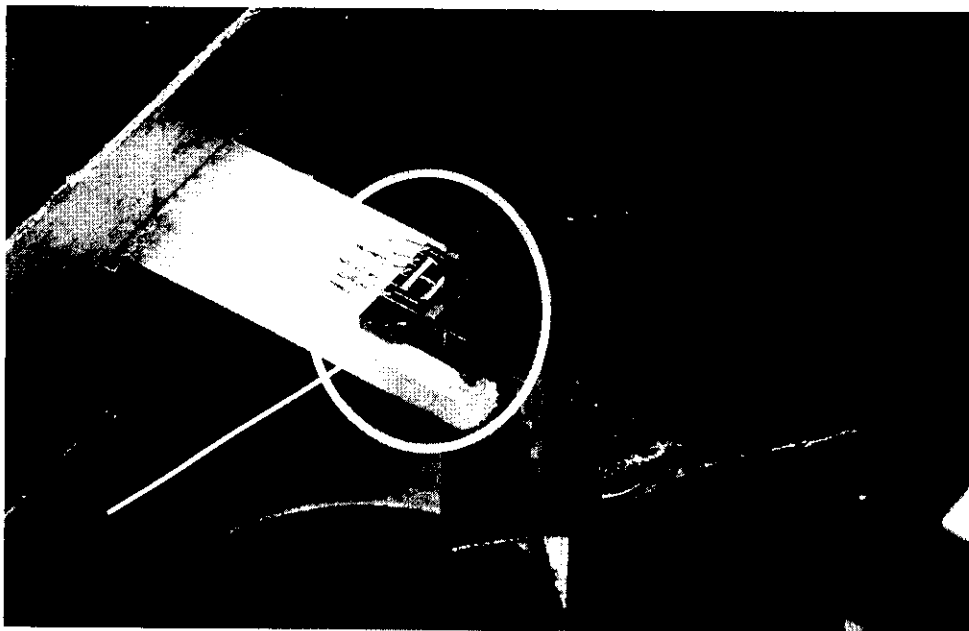


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Setup



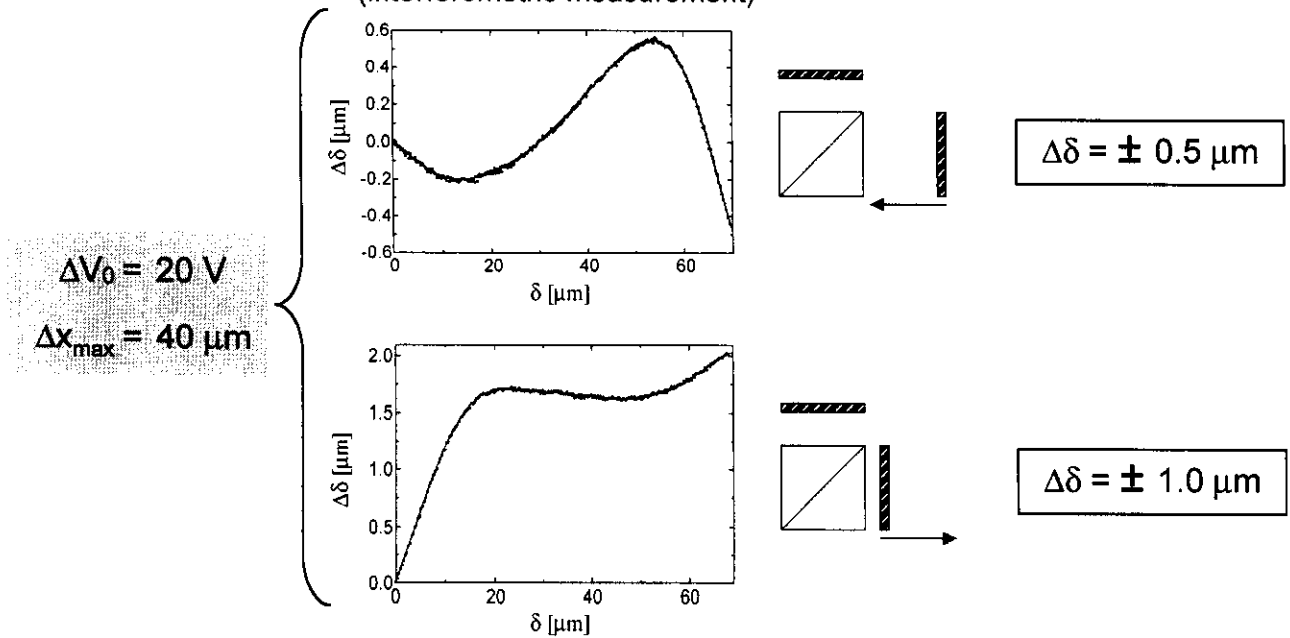
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Linearity

Variation of the optical path difference: $\Delta\delta$
(interferometric measurement)

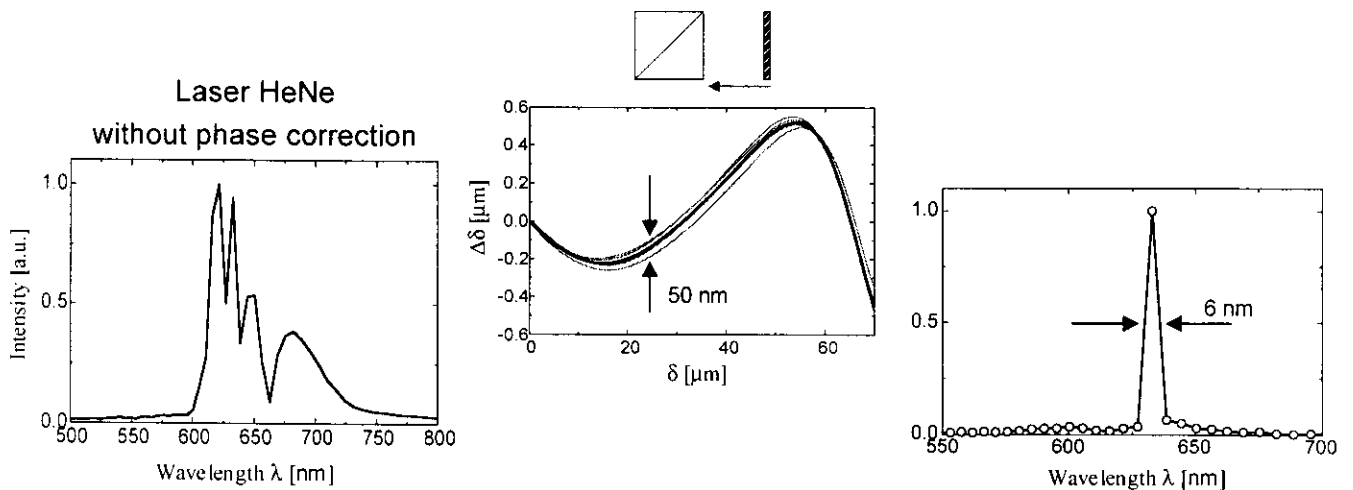


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Phase correction for calibrated mirror motion



$$B(\sigma) = \sum_{\delta} I_R(\delta) e^{-i2\pi\sigma\delta}$$

$$B(\sigma) = \sum_{\delta} I_R(\delta) e^{-i2\pi\sigma(\delta + \Delta\delta(\delta))}$$



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Chemical chip

(for fluorescence detection)

J.-Ch Roulet

Institute of Microtechnology University of Neuchâtel

<http://www-imt.unine.ch/>

Acknowledgment: K. Fluri, E. Verpoorte, R. Völkel,
H. P. Herzig¹, N.F. de Rooij, R. Dändliker

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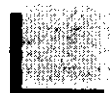
Introduction

Fluorescence detection with micro-optics:

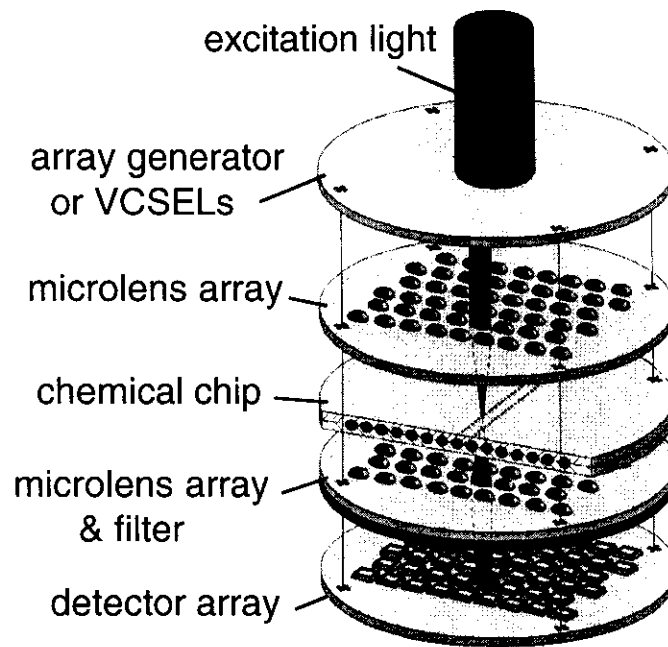
- Focusing excitation light into a detection volume (capillary, detection cell)
- Collection of the fluorescence
- Separation of the fluorescence (signal) from the noise (excitation light)

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Stacked μ TAS system



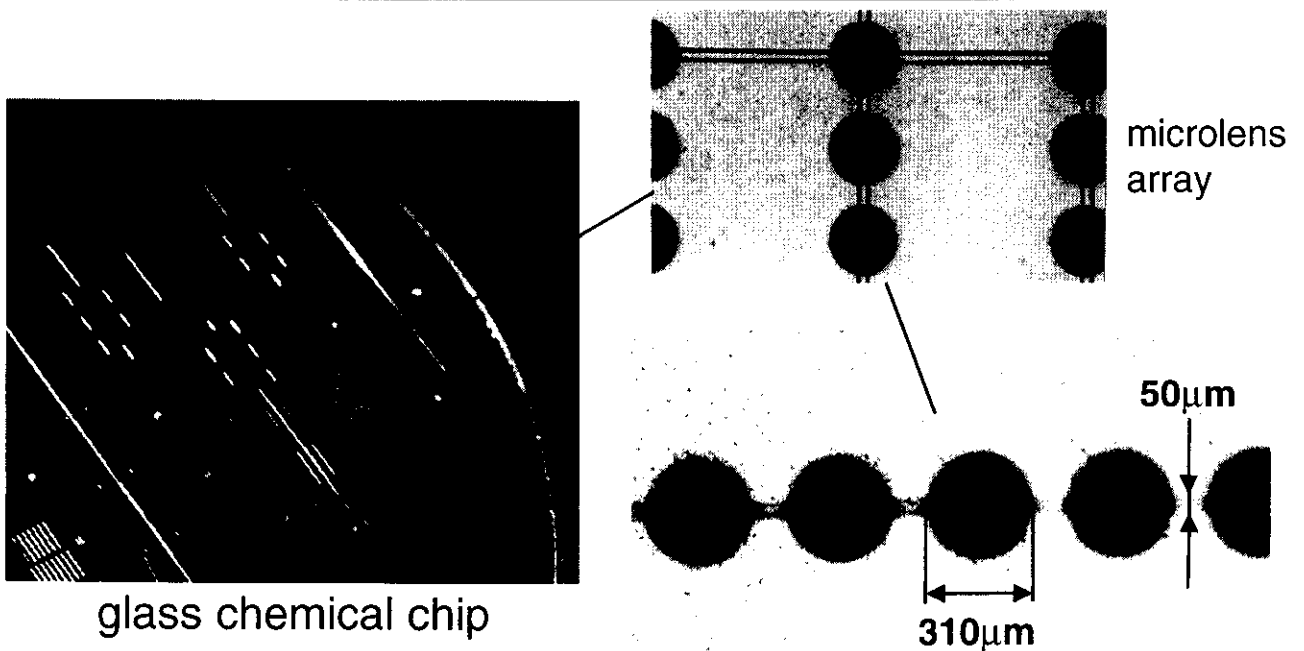
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INSTITUTE OF MICROT TECHNOLOGY

Transducers'99, Sandai (Japan)

J.-C. Roulet June 7-10 1999

Microlenses on sealed capillary

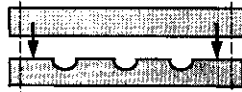


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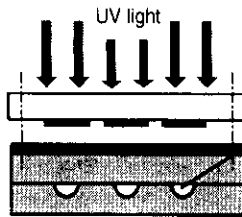
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Chemical chip and microlens array fabrication

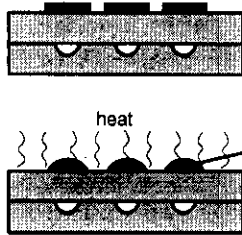
1. chemical chip bonding



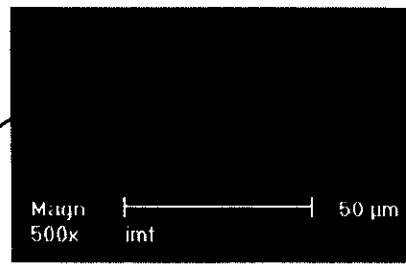
2. photolithographic process for microlens layer



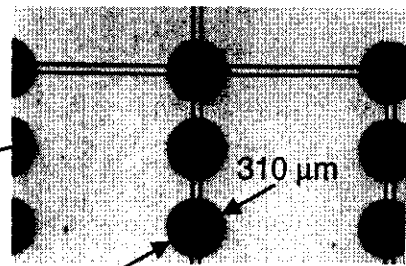
3. melting process



cross section of a capillary



microlens array

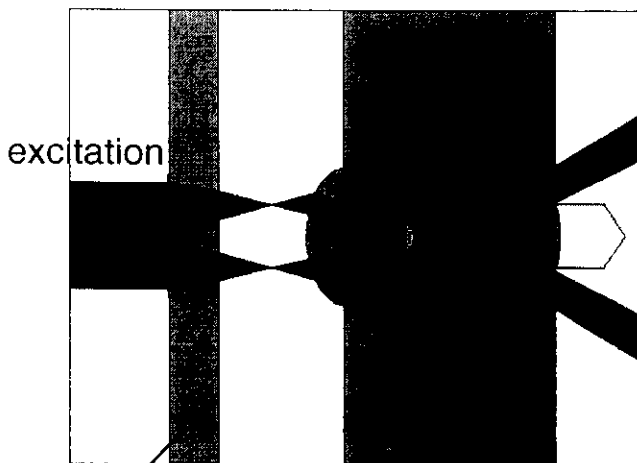


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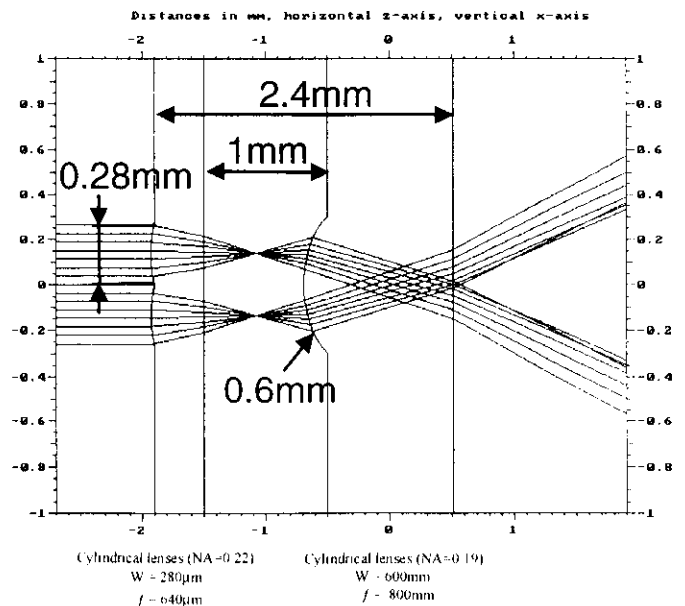
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Beam splitting illumination system

Raytrace Simulation



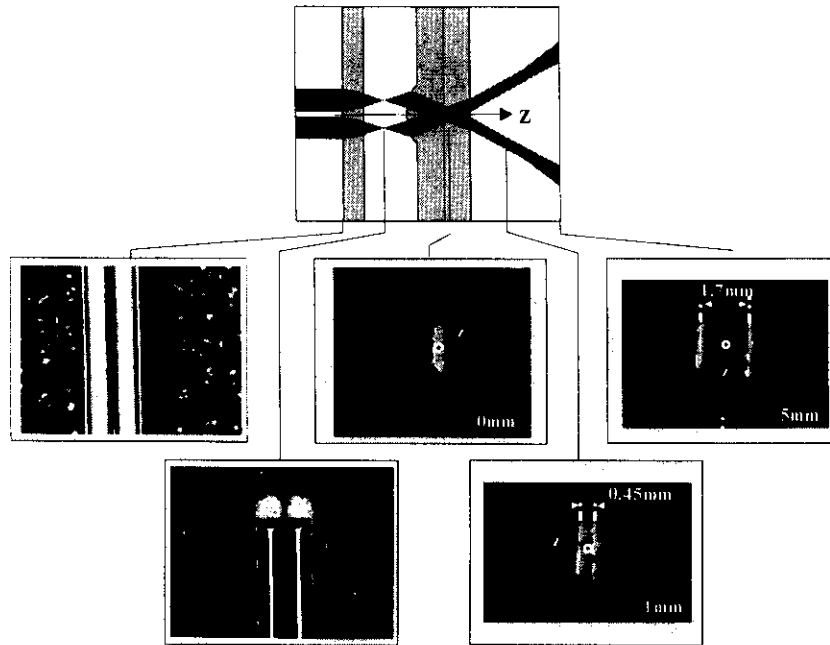
1st micro-lenses layer chemical chip with 2nd optical layer



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Beam splitting illumination system

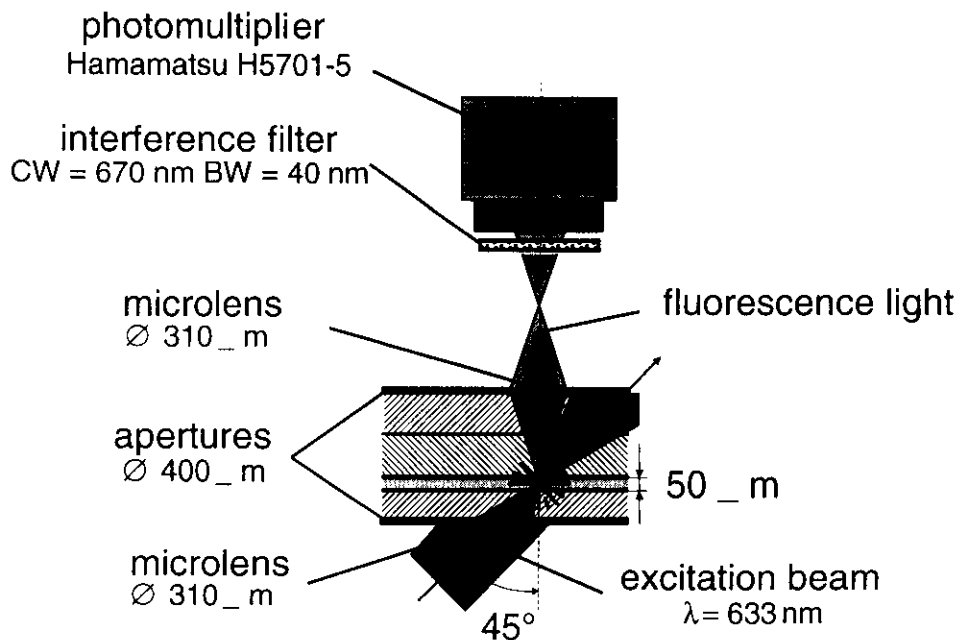


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Detection using microlens array



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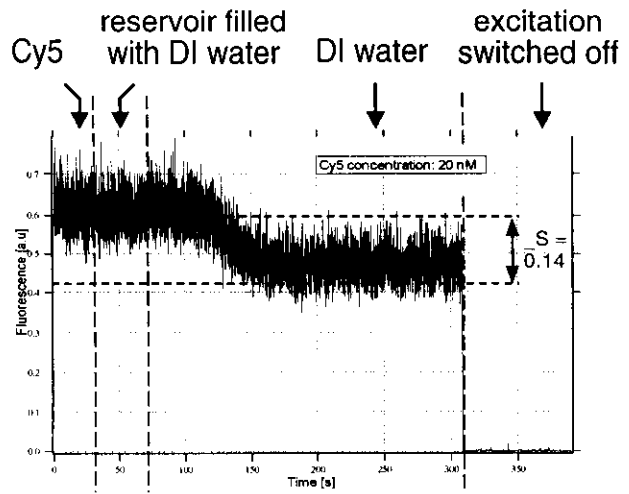
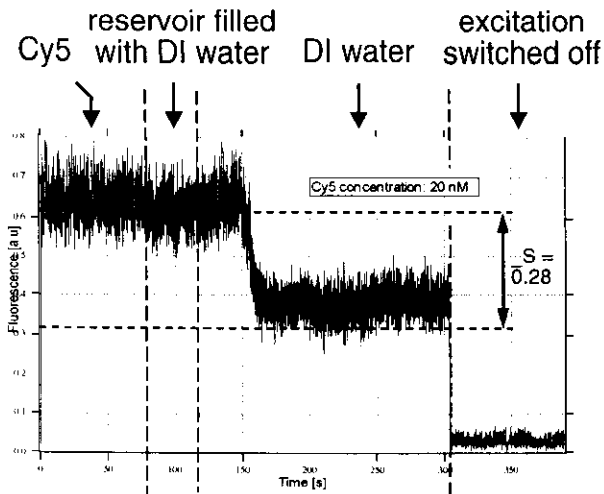


Measurement results

($T_i = 1/10$ s)

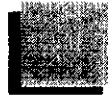
collection with microscope objective

collection with microlens



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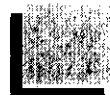


Conclusion

- chemical chip and optical system integration \Rightarrow route to detection in closely packed microchannels
- 20 nM dye solution detection \Rightarrow SNR = 20 dB/Hz
- integration of apertures and field stops possible \Rightarrow sensitivity improved
- versatile technology \Rightarrow integrated optical systems with different elements

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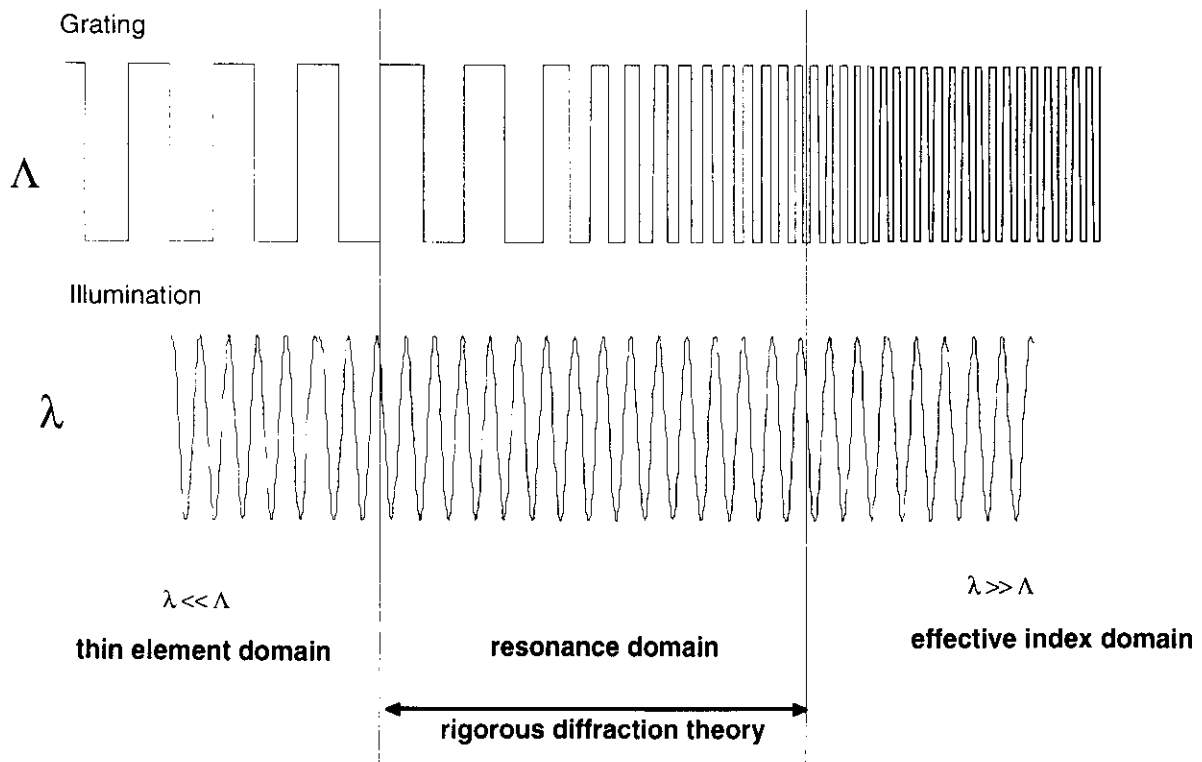
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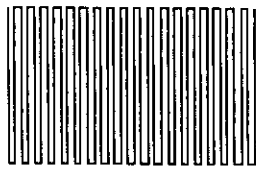
Optical Nanostructures

- Zero-order gratings
- Fabrication of optical nanostructures
 - optical lithography
 - e-beam lithography
 - self-assembling
- SNOM (scanning near-field optical microscopy)
- HRIM (high-resolution interferometric microscopy)

Diffraction theory for gratings

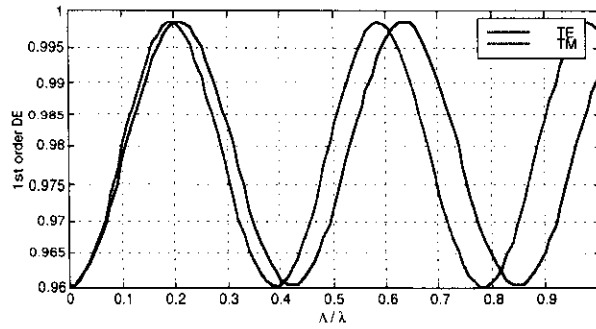


zero-order grating



ϵ_{eff}

$$\Lambda = 0.1 \lambda$$



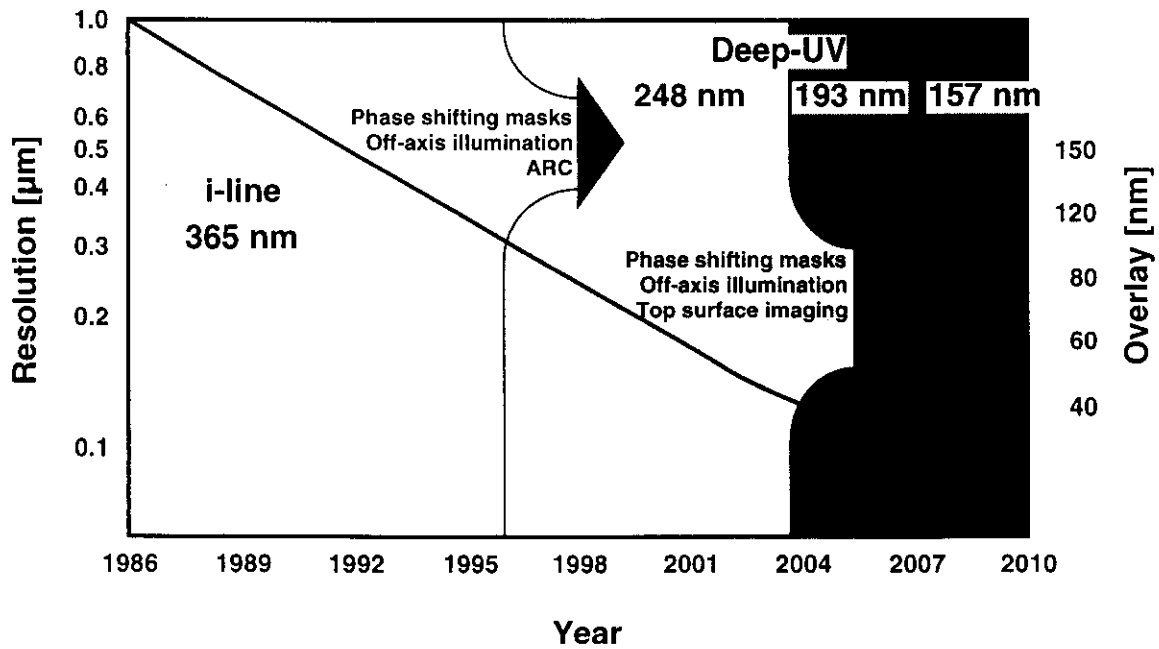
TE-polarization $\epsilon_{eff}^{TE} = t\epsilon_1 + (1-t)\epsilon_2$

TM-polarization $\frac{1}{\epsilon_{eff}^{TM}} = \frac{t}{\epsilon_1} + \frac{(1-t)}{\epsilon_2}$



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Optical lithography

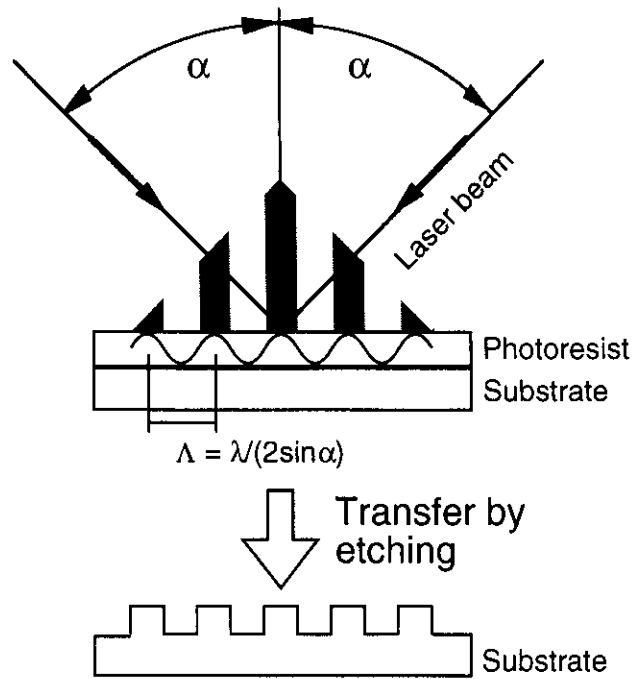


S. Wittekoek, Microelectronic Engineering 23 (1994)

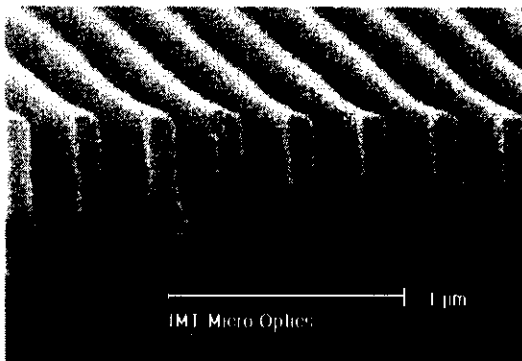


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Interferometric recording



Gratings recorded in photoresist



The LION LV-1 e-beam lithography tool



Lithography System for Integrated Optics and Nanostructures

Low Voltage 1 keV

C. David

Laboratory for Micro- and Nanotechnology,
Paul Scherrer Institute

Exposure of Bézier-curves in continuous path control (CPC) mode

CPC mode:

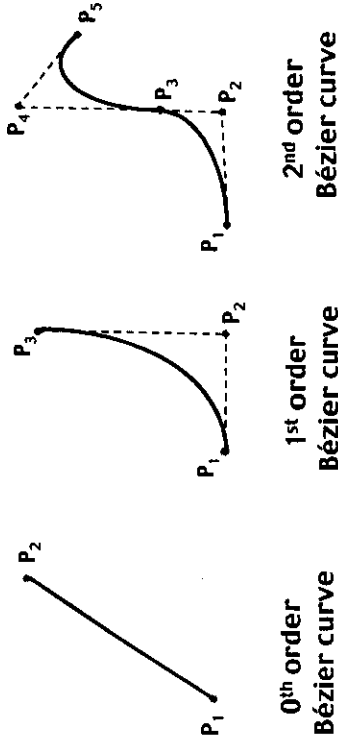
- Sample stage moves along (curved or straight) path (max. 2 mm/sec)
- Beam deflection only compensates for stage misplacement => no field stitching required

Bézier curves:

- Curves are not described by polygons or primitives



- => Optically smooth edges
- => Very efficient data compression

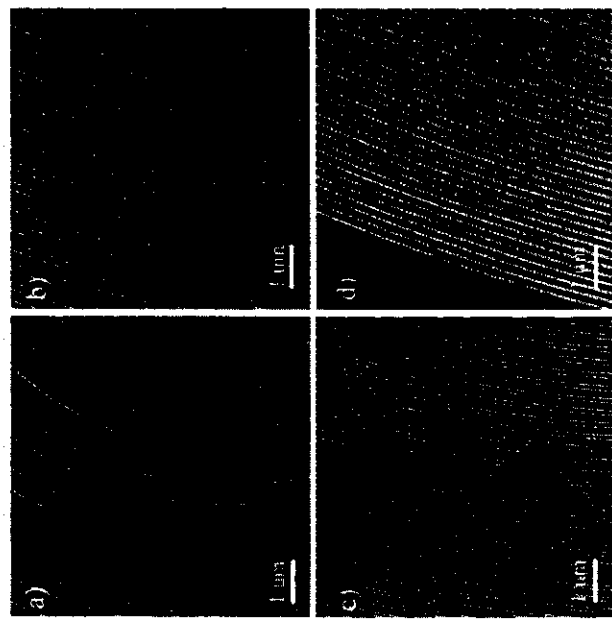


0th order
Bézier curve

1st order
Bézier curve

2nd order
Bézier curve

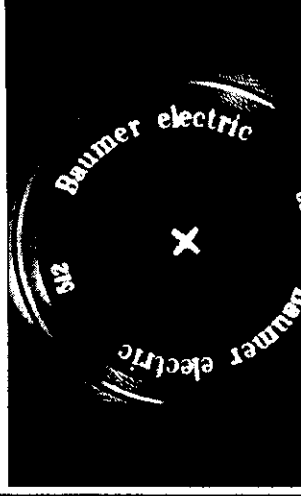
SEM micrograph of zone plate pattern



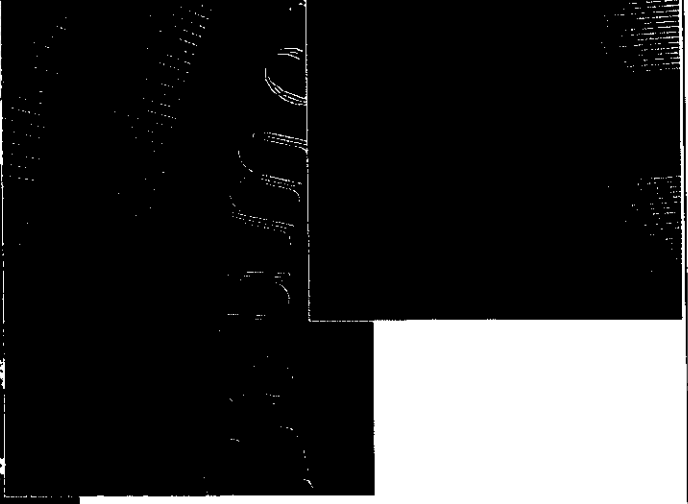
- Zone plate structures exposed at 2.5 keV in 50 nm PMMA etched into 20 nm Cr by RIE
- Each zone exposed as one single line in CPC-mode
- Good control of line width by defocusing down to 100 nm (duty cycle close to 0.5 for all line widths)

Applications: an angular encoder disk master

(patented by BAUMER electric, KTI-Projectpartner)

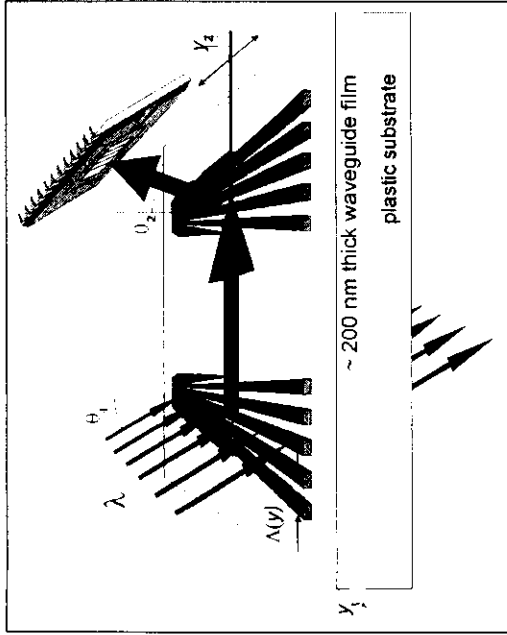


- approx. 1 cm diameter
- 45.000 line structures
- linewidths from 12 μm to 0.7 μm
- exposure time: 6 hours



Applications: chirped gratings for waveguide sensors

in collaboration with J. Söchtig and M.I. Gale, CSEM-Z



position γ_2 of output signal depends on:

- wavelength \Rightarrow miniaturized spectrometer
- waveguide film \Rightarrow
 - surface sensor for immunosensors
 - ion detection in liquids



- zone plates made from Si <111> by e-beam lithography and RIE
- Smallest structures: 100 nm wide, 1000 nm deep
- Maximum size: 1 cm long, 1 mm wide, 2500 zone structures

\Rightarrow focal length 1 m @ 0.1 nm wavelength



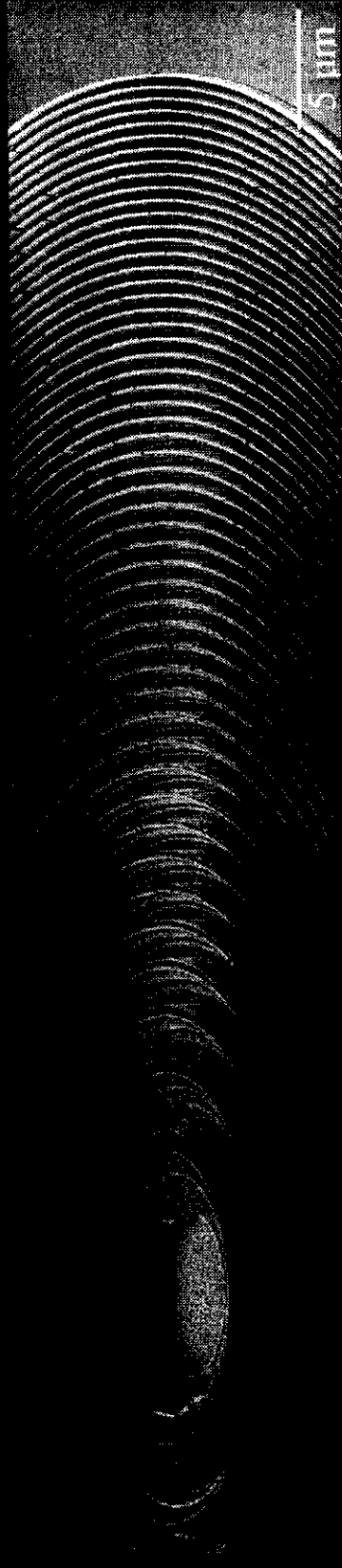
50nm PMMA
15nm Cr
Si <111>

e-beam exposure and development

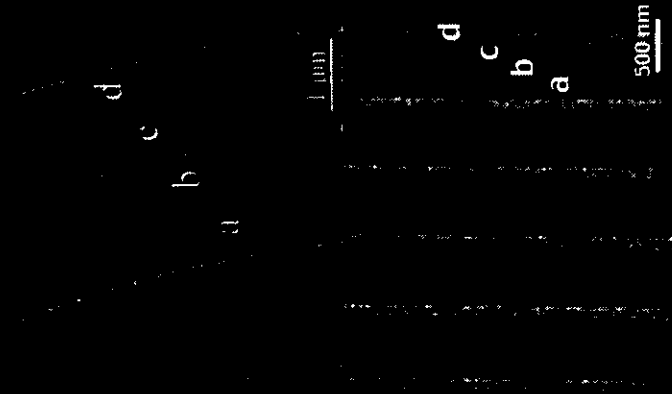
RIE Cl₂ + CO₂

RIE O₂ + CHF₃ + SF₆

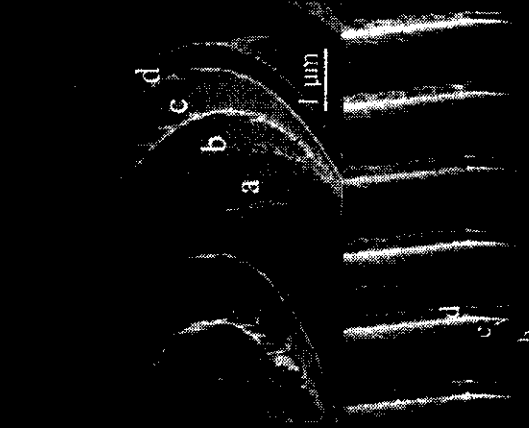
1 μm



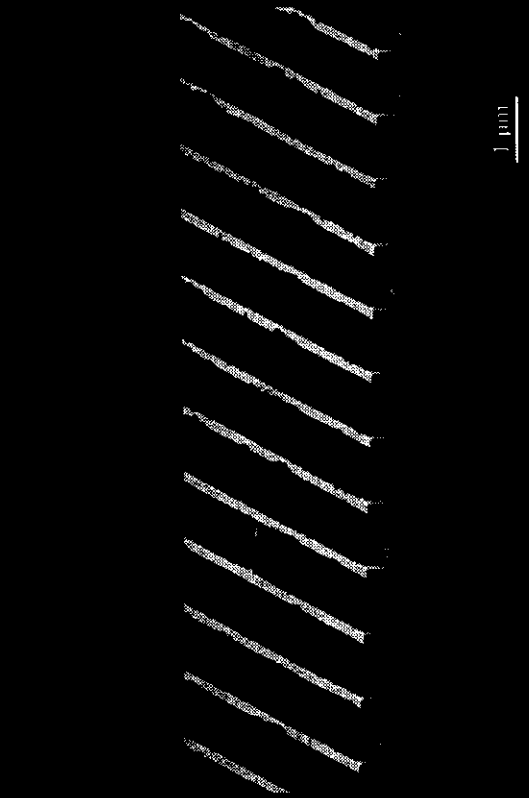
4-level x-ray lens with 1.5 mm structure height and 480 nm outermost pitch



Al and Cr mask structures:
a: no metal, b: only Cr,
c: only Al, d: Al on Cr

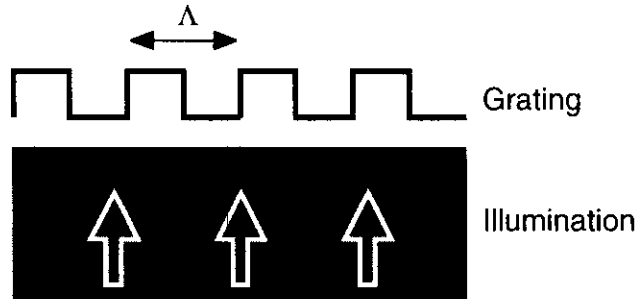
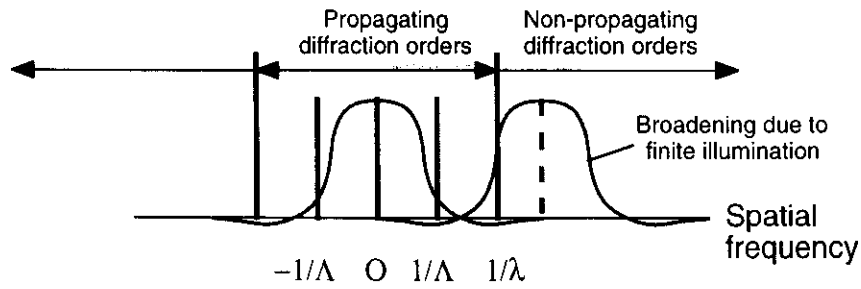


Resulting Si-structures
after RIE in $CHF_3/SF_6/O_2$



Blazed grating in quartz with a 4-level profil
etched in a CHF_3/O_2 plasma.

What can you see?

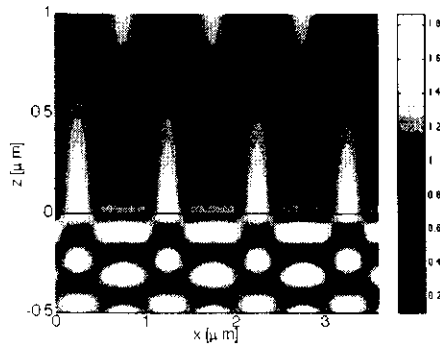


Amplitude

Optical near field

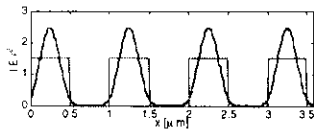
Phase

Example of calculated near-field intensity distribution

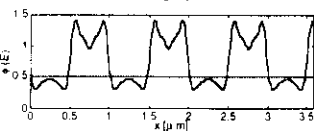


Chromium on glass mask: 50 nm layer, $1\mu\text{m}$ grating period, TE-pol., $\lambda = 633\text{ nm}$

The rigorous calculated field is **not** a binary function

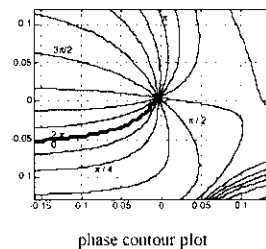


The phase is **not** constant inside the apertures



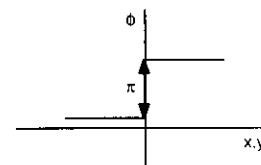
Intensity and phase in the output plane

Example of phase dislocation

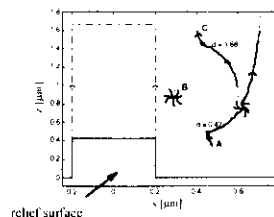


phase contour plot

Scan through the singularity



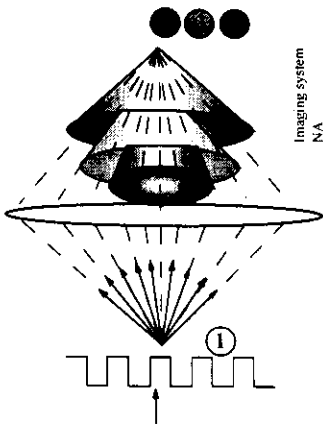
There is always a π phase jump scanning through a phase dislocation. The jump is sharp.



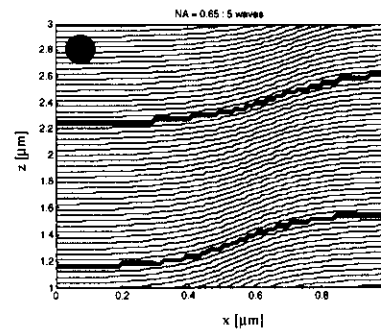
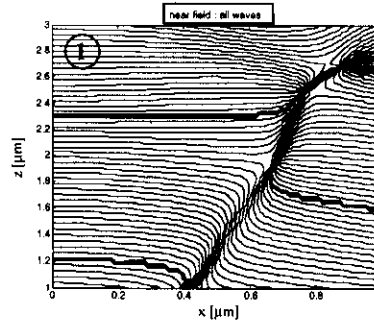
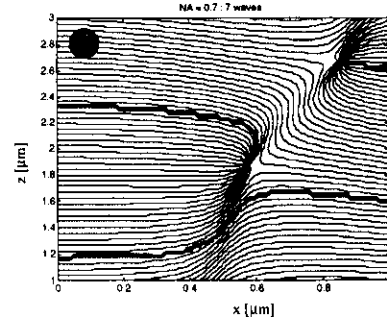
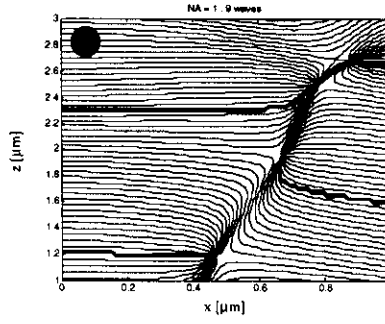
relief surface

Position of the phase dislocation for different grating depths

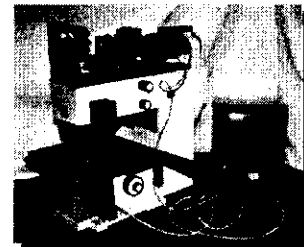
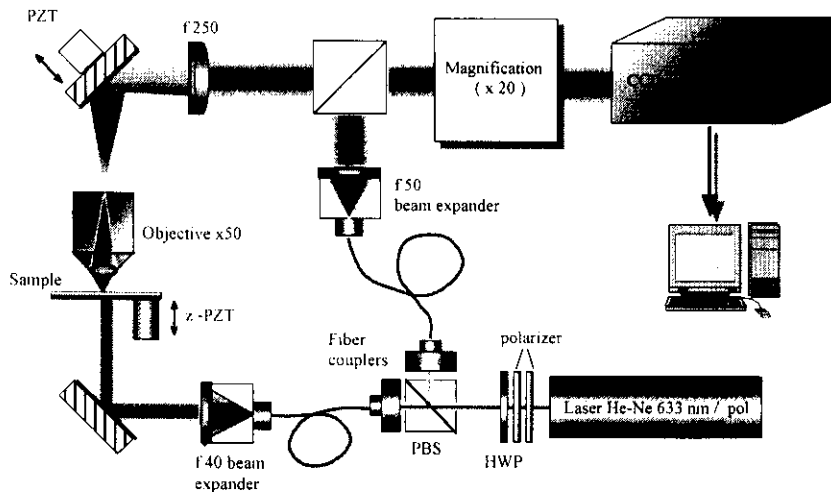
Far-field phase dislocations after low-pass filtering



Measuring the phase in the far field can give some information about the geometry of the structure!



High Resolution Interference Microscope

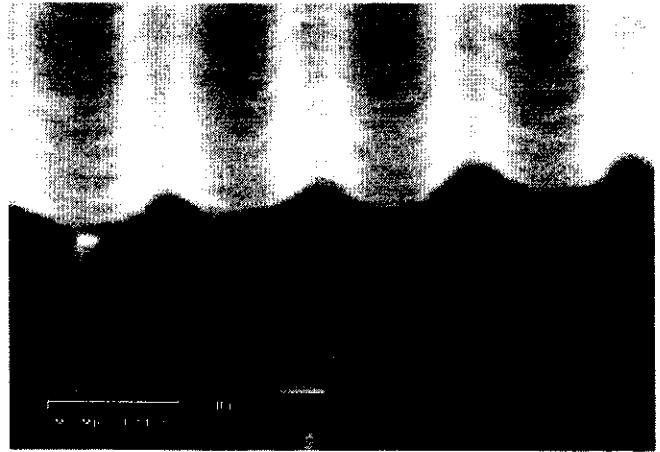


Mach-Zender interferometer

HRIM based on a Mach-Zender interferometer

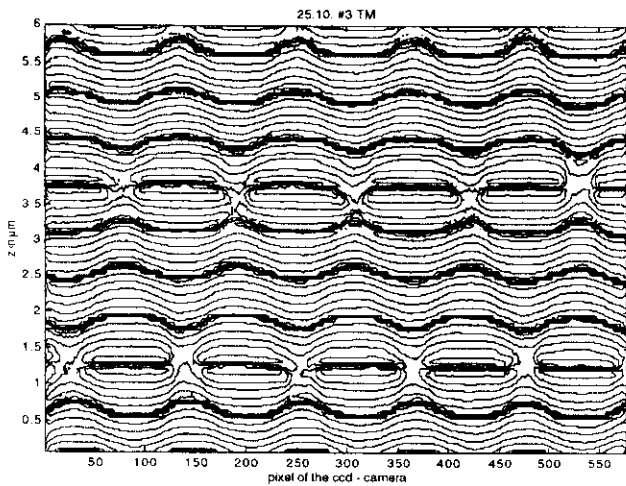
- CCD-pixel size: 10 μm
- Object-pixel size: 10 nm

SEM pictures

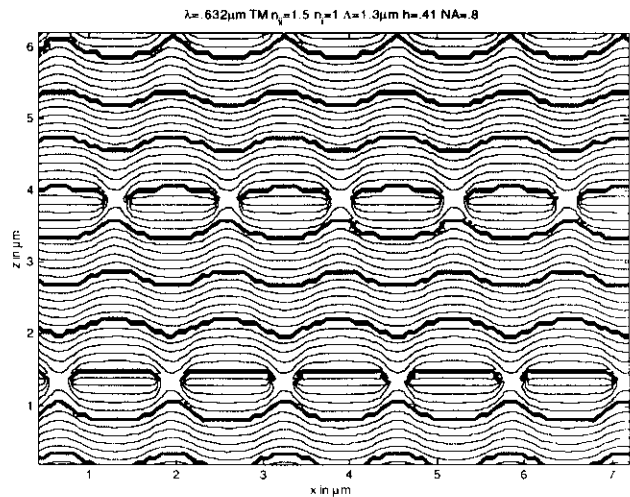


16/12/99

measurement / calculation



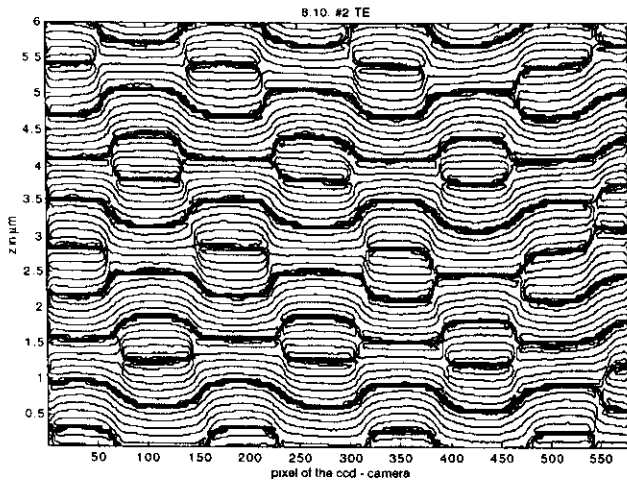
1 pixel of the ccd-camera = 10nm



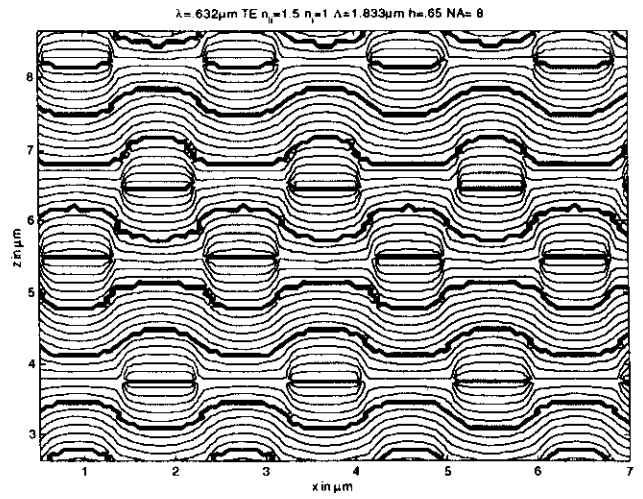
$\Lambda = 1.3\mu\text{m}$ $h = 0.41\mu\text{m}$ TM
 $n_{ii} = 1.5$ $n_i = 1$ $\lambda = 0.632\mu\text{m}$ NA = 0.8

16/12/99

measurement / calculation



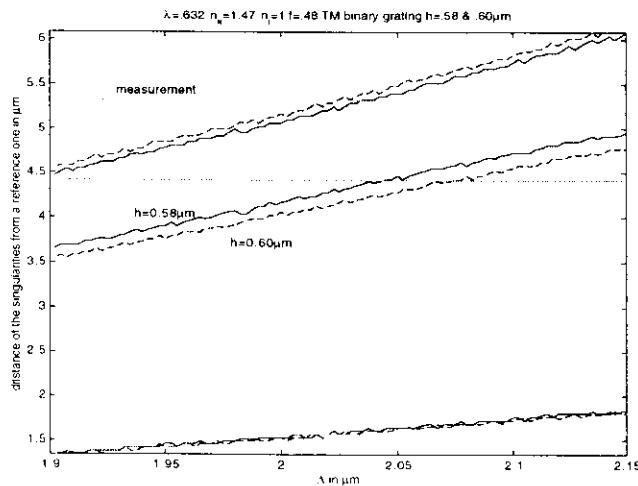
1 pixel of the ccd-camera = 10nm



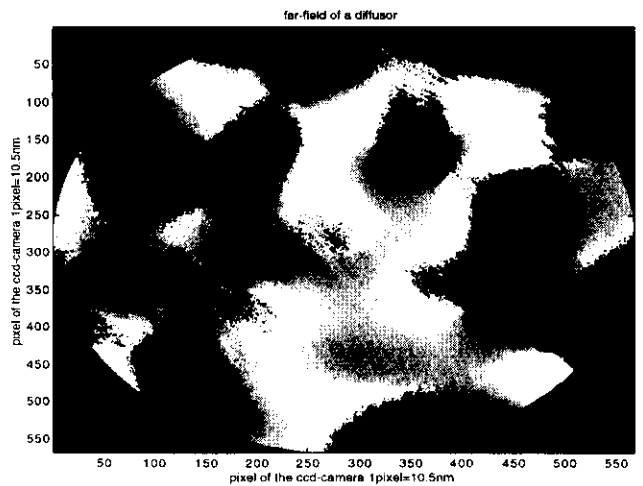
$\Lambda = 1.833 \mu\text{m}$ $h = 0.65 \mu\text{m}$ TE

$n_{ii} = 1.5$ $n_t = 1$ $\lambda = 632 \mu\text{m}$ $NA = 0.8$

Resolution

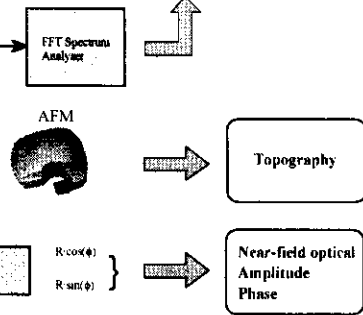
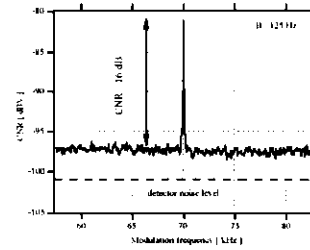
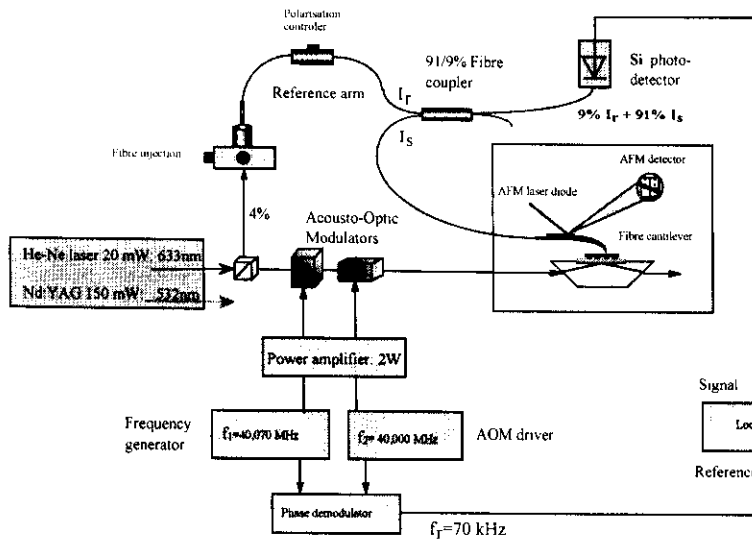


distances of phase singularities
in the far field of a grating
 $\Delta z \approx 60 \text{nm}$



speckle
 $\Delta x = \Delta y \approx 20 \text{nm}$

Heterodyne detection system for PSTM measurements



Bent coated fiber cantilever

Why heterodyne detection?

- Interferometry for phase measurements.
- Low signal detection.
- $P_{ref} \gg P_{obj} \Rightarrow SNR = \frac{S}{q \cdot B} \cdot P_{obj}$
- Sensitive detection method.
(more than an avalanche photodiode detection)

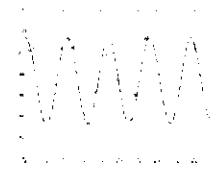
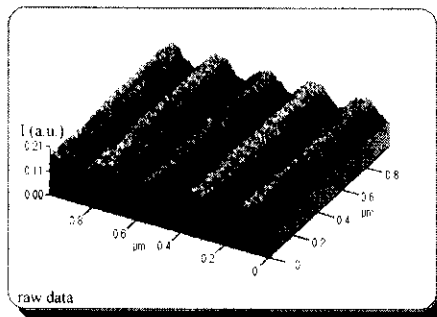
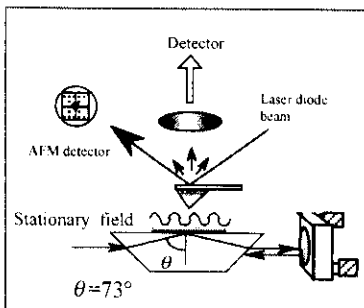


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Measurements with transparent AFM probe

Evanescent standing wave field



$$\Lambda_{th} = \frac{\lambda/n_s}{2 \cdot \sin(\theta)} = 219.1 \text{ nm}$$

$$\Lambda_{exp} = 220 \text{ nm} \pm 1 \text{ nm} \leftrightarrow \theta = 72^\circ \pm 1^\circ$$

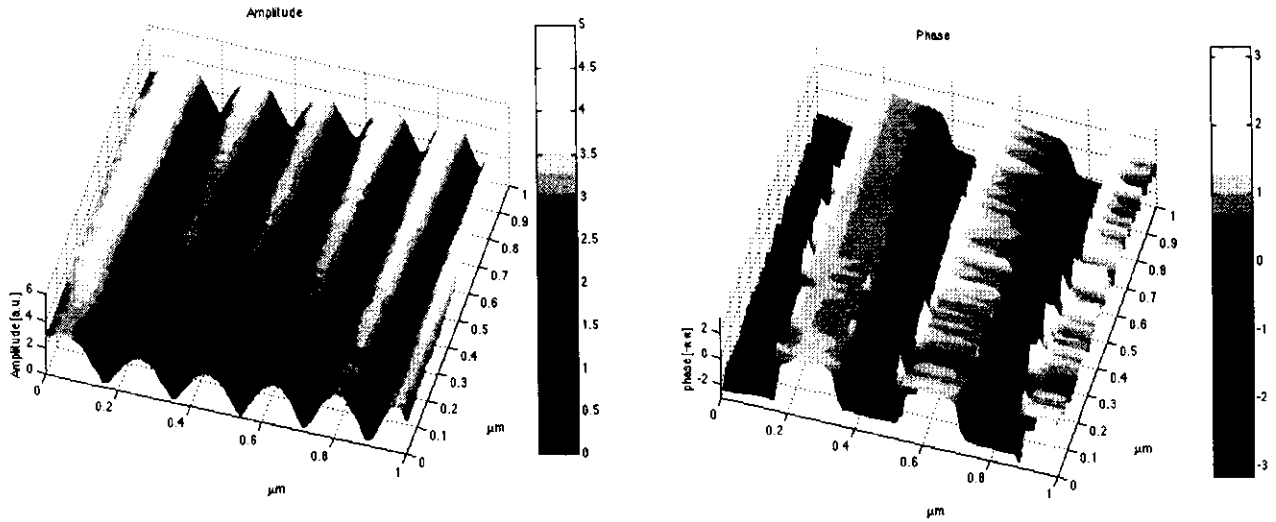
$$\lambda = 633 \text{ nm}$$



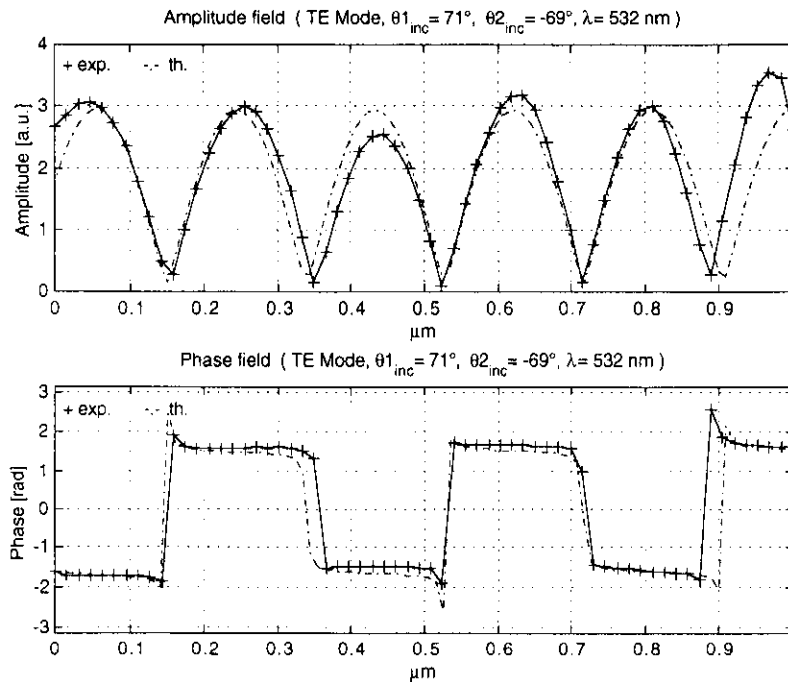
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Amplitude and phase measurement of evanescent standing wave

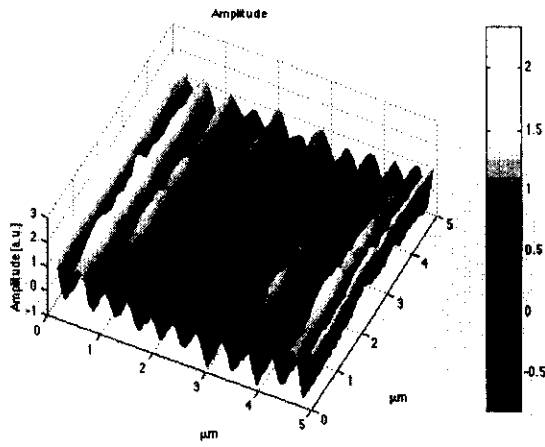


Amplitude and phase of evanescent standing wave



1 μm grating at normal incidence

TE-mode



TM-mode

